

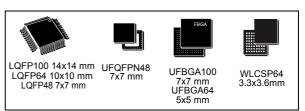
# STM32F098CC STM32F098RC STM32F098VC

ARM®-based 32-bit MCU, 256 KB Flash, CAN, 12 timers, ADC, DAC & comm. interfaces, 1.8 V

Datasheet - production data

#### **Features**

- Core: ARM<sup>®</sup> 32-bit Cortex<sup>®</sup>-M0 CPU, frequency up to 48 MHz
- Memories
  - 256 Kbytes of Flash memory
  - 32 Kbytes of SRAM with HW parity
- CRC calculation unit
- · Reset and power management
  - Digital & I/Os supply:  $V_{DD}$  = 1.8 V ± 8%
  - Analog supply: V<sub>DDA</sub> = V<sub>DD</sub> to 3.6 V
  - Selected I/Os:  $V_{DDIO2}$  = 1.65 V to 3.6 V
  - Low power modes: Sleep, Stop
  - V<sub>BAT</sub> supply for RTC and backup registers
- Clock management
  - 4 to 32 MHz crystal oscillator
  - 32 kHz oscillator for RTC with calibration
  - Internal 8 MHz RC with x6 PLL option
  - Internal 40 kHz RC oscillator
  - Internal 48 MHz oscillator with automatic trimming based on ext. synchronization
- Up to 87 fast I/Os
  - All mappable on external interrupt vectors
  - Up to 68 I/Os with 5V-tolerant capability and 19 with independent supply V<sub>DDIO2</sub>
- 12-channel DMA controller
- One 12-bit, 1.0 µs ADC (up to 16 channels)
  - Conversion range: 0 to 3.6 V
  - Separate analog supply: 2.4 V to 3.6 V
- One 12-bit D/A converter (with 2 channels)
- Two fast low-power analog comparators with programmable input and output
- Up to 23 capacitive sensing channels for touchkey, linear and rotary touch sensors
- Calendar RTC with alarm and periodic wakeup from Stop/Standby



#### 12 timers

- One 16-bit advanced-control timer for 6 channel PWM output
- One 32-bit and seven 16-bit timers, with up to 4 IC/OC, OCN, usable for IR control decoding or DAC control
- Independent and system watchdog timers
- SysTick timer
- Communication interfaces
  - Two I<sup>2</sup>C interfaces supporting Fast Mode Plus (1 Mbit/s) with extra current sink, one supporting SMBus/PMBus and wakeup
  - Up to eight USARTs supporting master synchronous SPI and modem control, three with ISO7816 interface, LIN, IrDA, auto baud rate detection and wakeup feature
  - Two SPIs (18 Mbit/s) with 4 to 16 programmable bit frames, and with I<sup>2</sup>S interface multiplexed
  - CAN interface
- HDMI CEC wakeup on header reception
- Serial wire debug (SWD)
- 96-bit unique ID
- All packages ECOPACK<sup>®</sup>2

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## 1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F098CC/RC/VC microcontrollers.

This document should be read in conjunction with the STM32F0xxxx reference manual (RM0091). The reference manual is available from the STMicroelectronics website <a href="https://www.st.com">www.st.com</a>.

For information on the ARM<sup>®</sup> Cortex<sup>®</sup>-M0 core, please refer to the Cortex<sup>®</sup>-M0 Technical Reference Manual, available from the www.arm.com website.





#### **Description** 2

The STM32F098CC/RC/VC microcontrollers incorporate the high-performance ARM® Cortex®-M0 32-bit RISC core operating at up to 48 MHz frequency, high-speed embedded memories (256 Kbytes of Flash memory and 32 Kbytes of SRAM), and an extensive range of enhanced peripherals and I/Os. The device offers standard communication interfaces (two I<sup>2</sup>Cs, two SPIs/one I<sup>2</sup>S, one HDMI CEC and up to eight USARTs), one CAN, one 12-bit ADC, one 12-bit DAC with two channels, seven 16-bit timers, one 32-bit timer and an advanced-control PWM timer.

The STM32F098CC/RC/VC microcontrollers operate in the -40 to +85 °C and -40 to +105 °C temperature ranges, at a 1.8 V ± 8% power supply. A comprehensive set of power-saving modes allows the design of low-power applications.

The STM32F098CC/RC/VC microcontrollers include devices in seven different package ranging from 48 pins to 100 pins with a die form also available upon request. Depending on the device chosen, different sets of peripherals are included.

These features make the STM32F098CC/RC/VC microcontrollers suitable for a wide range of applications such as application control and user interfaces, hand-held equipment, A/V receivers and digital TV, PC peripherals, gaming and GPS platforms, industrial applications, PLCs, inverters, printers, scanners, alarm systems, video intercoms and HVACs.

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Table 1. STM32F098CC/RC/VC family device features and peripheral counts

Perip	oheral	STM32F098CC	STM32F098RC	STM32F098VC		
Flash memory (Kbyte)		256				
SRAM (Kbyte)		32				
Advanced control		1 (16-bit)				
Timers	General purpose		5 (16-bit) 1 (32-bit)			
	Basic					
	SPI [I <sup>2</sup> S] <sup>(1)</sup>		2 [2]			
	I <sup>2</sup> C		2			
Comm. interfaces	USART	6	8	3		
III.OII.GOO	CAN	1				
	CEC	1				
	t ADC f channels)	1 (10 ext. + 3 int.)				
	t DAC f channels)	1 (2)				
Analog co	omparator	2				
GP	PIOs	37	51	87		
Capacitive sensing channels		16	17	23		
Max. CPU frequency		48 MHz				
Operating voltage		$V_{DD}$ = 1.8 V ± 8%, $V_{DDA}$ = from $V_{DD}$ to 3.6 V				
Operating temperature		Ambient operating temperature: -40°C to 85°C / -40°C to 105°C Junction temperature: -40°C to 105°C / -40°C to 125°C				
Packages		LQFP48 UFQFPN48	LQFP64 UFBGA64 WLCSP64	LQFP100 UFBGA100		

<sup>1.</sup> The SPI interface can be used either in SPI mode or in I<sup>2</sup>S audio mode.

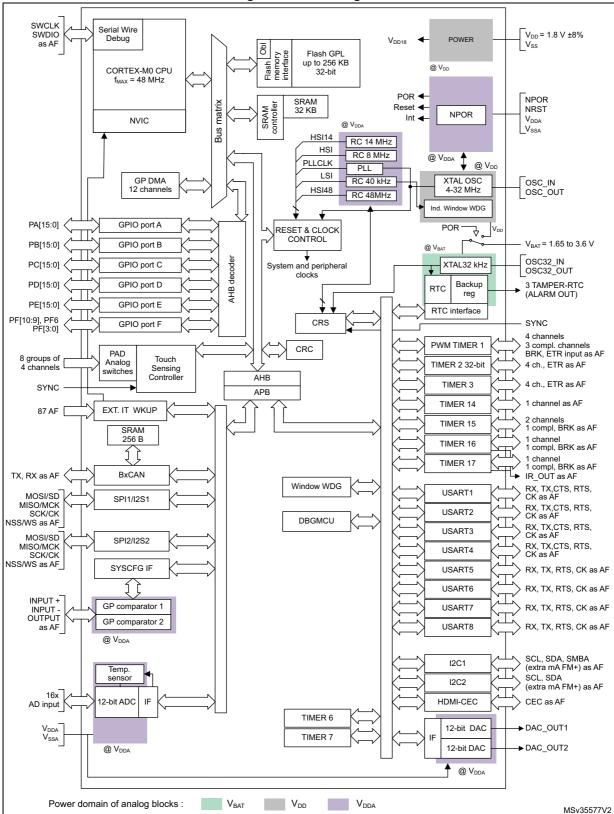


Figure 1. Block diagram



### 3 Functional overview

Figure 1 shows the general block diagram of the STM32F098CC/RC/VC devices.

## 3.1 ARM®-Cortex®-M0 core

The ARM<sup>®</sup> Cortex<sup>®</sup>-M0 is a generation of ARM 32-bit RISC processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM<sup>®</sup> Cortex<sup>®</sup>-M0 processors feature exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The STM32F098CC/RC/VC devices embed ARM core and are compatible with all ARM tools and software.

#### 3.2 Memories

The device has the following features:

- 32 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states and featuring embedded parity checking with exception generation for fail-critical applications.
- The non-volatile memory is divided into two arrays:
  - 256 Kbytes of embedded Flash memory for programs and data
  - Option bytes

The option bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (Cortex<sup>®</sup>-M0 serial wire) and boot in RAM selection disabled

#### 3.3 Boot modes

At startup, the boot pin and boot selector option bits are used to select one of the three boot options:

- boot from User Flash memory
- boot from System Memory
- boot from embedded SRAM

The boot pin is shared with the standard GPIO and can be disabled through the boot selector option bits. The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART on pins PA14/PA15 or PA9/PA10 or I<sup>2</sup>C on pins PB6/PB7.



## 3.4 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

## 3.5 Power management

#### 3.5.1 Power supply schemes

- V<sub>DD</sub> = V<sub>DDIO1</sub> = 1.8 V ± 8%: external power supply for I/Os (V<sub>DDIO1</sub>) and digital logic. It is provided externally through VDD pins.
- V<sub>DDA</sub> = from V<sub>DD</sub> to 3.6 V: external analog power supply for ADC, DAC, RCs and PLL (minimum voltage to be applied to V<sub>DDA</sub> is 2.4 V when the ADC or DAC are used). It is provided externally through VDDA pin. The V<sub>DDA</sub> voltage level must be always greater or equal to the V<sub>DD</sub> voltage level and must be established first.
- V<sub>DDIO2</sub> = 1.65 to 3.6 V: external power supply for marked I/Os. V<sub>DDIO2</sub> is provided externally through the VDDIO2 pin. The V<sub>DDIO2</sub> voltage level is completely independent from V<sub>DD</sub> or V<sub>DDA</sub>, but it must not be provided without a valid supply on V<sub>DD</sub>. The V<sub>DDIO2</sub> supply is monitored and compared with the internal reference voltage (V<sub>REFINT</sub>). When the V<sub>DDIO2</sub> is below this threshold, all the I/Os supplied from this rail are disabled by hardware. The output of this comparator is connected to EXTI line 31 and it can be used to generate an interrupt. Refer to the pinout diagrams or tables for concerned I/Os list.
- V<sub>BAT</sub> = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V<sub>DD</sub> is not present.

For more details on how to connect power pins, refer to Figure 13: Power supply scheme.

#### 3.5.2 Power-on reset

To guarantee a proper power-on reset, the NPOR pin must be held low until  $V_{DD}$  is stable. When  $V_{DD}$  is stable, the reset state can be exited either by:

- putting the NPOR pin in high impedance (NPOR pin has an internal pull-up), or by
- forcing the pin to high level by connecting it to V<sub>DDA</sub>

### 3.5.3 Low-power modes

The STM32F098CC/RC/VC microcontrollers support two low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

#### Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.



#### Stop mode

Stop mode achieves very low power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled.

The device can be woken up from Stop mode by any of the EXTI lines. The EXTI line source can be one of the 16 external lines, RTC, I2C1 USART1, USART3, COMPx. The CEC, USART1, USART2, USART3 and I2C1 peripherals can be configured to enable the HSI RC oscillator so as to get clock for processing incoming data.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop mode.

### 3.6 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-32 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the application to configure the frequency of the AHB and the APB domains. The maximum frequency of the AHB and the APB domains is 48 MHz.

Additionally, also the internal RC 48 MHz oscillator can be selected for system clock or PLL input source. This oscillator can be automatically fine-trimmed by the means of the CRS peripheral using the external synchronization.



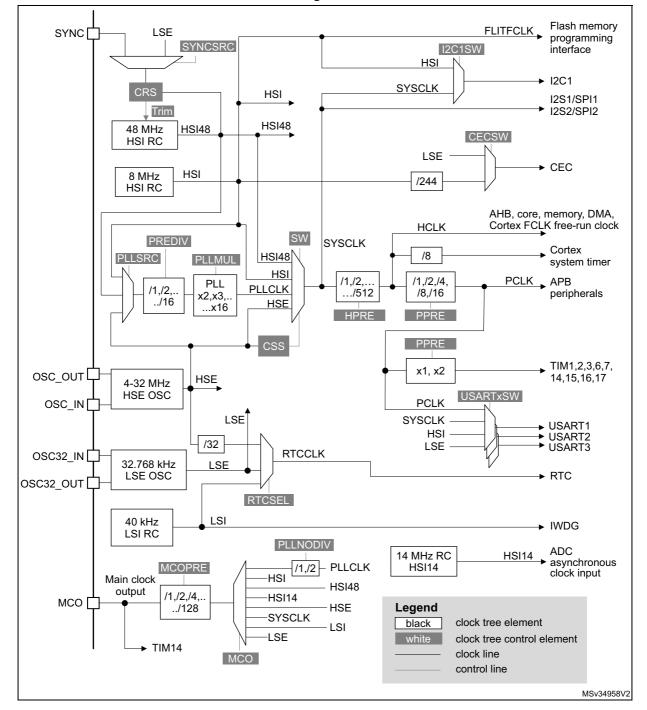


Figure 2. Clock tree

## 3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions.



The I/O configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

### 3.8 Direct memory access controller (DMA)

The 12-channel general-purpose DMAs (seven channels for DMA1 and five channels for DMA2) manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers.

The DMAs support circular buffer management, removing the need for user code intervention when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and transfer sizes between source and destination are independent.

DMA can be used with the main peripherals: SPIx, I2Sx, I2Cx, USARTx, all TIMx timers (except TIM14), DAC and ADC.

## 3.9 Interrupts and events

#### 3.9.1 Nested vectored interrupt controller (NVIC)

The STM32F0xx family embeds a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels (not including the 16 interrupt lines of Cortex -M0) and 4 priority levels.

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of late arriving higher priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

#### 3.9.2 Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 32 edge detector lines used to generate interrupt/event requests and wake-up the system. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the internal clock period. Up to 87 GPIOs can be connected to the 16 external interrupt lines.

## 3.10 Analog-to-digital converter (ADC)

The 12-bit analog-to-digital converter has up to 16 external and 3 internal (temperature sensor, voltage reference, VBAT voltage measurement) channels and performs conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

#### 3.10.1 Temperature sensor

The temperature sensor (TS) generates a voltage V<sub>SENSE</sub> that varies linearly with temperature.

The temperature sensor is internally connected to the ADC\_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at a temperature of 30 °C ( $\pm$ 5 °C), V <sub>DDA</sub> = 3.3 V ( $\pm$ 10 mV)	0x1FFF F7B8 - 0x1FFF F7B9
TS_CAL2	TS ADC raw data acquired at a temperature of 110 °C (±5 °C), V <sub>DDA</sub> = 3.3 V (±10 mV)	0x1FFF F7C2 - 0x1FFF F7C3

Table 2. Temperature sensor calibration values

## 3.10.2 Internal voltage reference (V<sub>REFINT</sub>)

The internal voltage reference ( $V_{REFINT}$ ) provides a stable (bandgap) voltage output for the ADC and comparators.  $V_{REFINT}$  is internally connected to the ADC\_IN17 input channel. The precise voltage of  $V_{REFINT}$  is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 3. Internal voltage reference calibration values

Calibration value name	Description	Memory address
	Raw data acquired at a temperature of 30 °C (±5 °C), V <sub>DDA</sub> = 3.3 V (±10 mV)	0x1FFF F7BA - 0x1FFF F7BB



#### 3.10.3 V<sub>BAT</sub> battery voltage monitoring

This embedded hardware feature allows the application to measure the  $V_{BAT}$  battery voltage using the internal ADC channel ADC\_IN18. As the  $V_{BAT}$  voltage may be higher than  $V_{DDA}$ , and thus outside the ADC input range, the  $V_{BAT}$  pin is internally connected to a bridge divider by 2. As a consequence, the converted digital value is half the  $V_{BAT}$  voltage.

## 3.11 Digital-to-analog converter (DAC)

The two 12-bit buffered DAC channels can be used to convert digital signals into analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in non-inverting configuration.

This digital Interface supports the following features:

- 8-bit or 12-bit monotonic output
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- Dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- External triggers for conversion

Six DAC trigger inputs are used in the device. The DAC is triggered through the timer trigger outputs and the DAC interface is generating its own DMA requests.

## 3.12 Comparators (COMP)

The device embeds two fast rail-to-rail low-power comparators with programmable reference voltage (internal or external), hysteresis and speed (low speed for low power) and with selectable output polarity.

The reference voltage can be one of the following:

- External I/O
- DAC output pins
- Internal reference voltage or submultiple (1/4, 1/2, 3/4). Refer to *Table 25: Embedded internal reference voltage* for the value and precision of the internal reference voltage.

Both comparators can wake up from STOP mode, generate interrupts and breaks for the timers and can be also combined into a window comparator.

## 3.13 Touch sensing controller (TSC)

The STM32F098CC/RC/VC devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 23 capacitive sensing channels distributed over 8 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (glass, plastic...). The capacitive variation



introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists in charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage, this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate. For operation, one capacitive sensing GPIO in each group is connected to an external capacitor and cannot be used as effective touch sensing channel.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library, which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

Table 4. Capacitive sensing GPIOs available on STM32F098CC/RC/VC devices

Group	Capacitive sensing signal name	Pin name
	TSC_G1_IO1	PA0
1	TSC_G1_IO2	PA1
'	TSC_G1_IO3	PA2
	TSC_G1_IO4	PA3
	TSC_G2_IO1	PA4
2	TSC_G2_IO2	PA5
2	TSC_G2_IO3	PA6
	TSC_G2_IO4	PA7
	TSC_G3_IO1	PC5
3	TSC_G3_IO2	PB0
	TSC_G3_IO3	PB1
	TSC_G4_IO1	PA9
4	TSC_G4_IO2	PA10
4	TSC_G4_IO3	PA11
	TSC_G4_IO4	PA12

Group	Capacitive sensing signal name	Pin name
	TSC_G5_IO1	PB3
5	TSC_G5_IO2	PB4
3	TSC_G5_IO3	PB6
	TSC_G5_IO4	PB7
	TSC_G6_IO1	PB11
6	TSC_G6_IO2	PB12
0	TSC_G6_IO3	PB13
	TSC_G6_IO4	PB14
	TSC_G7_IO1	PE2
7	TSC_G7_IO2	PE3
,	TSC_G7_IO3	PE4
	TSC_G7_IO4	PE5
	TSC_G8_IO1	PD12
8	TSC_G8_IO2	PD13
0	TSC_G8_IO3	PD14
	TSC_G8_IO4	PD15

Table 5. Number of capacitive sensing channels available on STM32F098CC/RC/VC devices

Analog I/O group	Number of capacitive sensing channels							
Analog I/O group	STM32F098Vx	STM32F098Rx	STM32F098Cx					
G1	3	3	3					
G2	3	3	3					
G3	2	2	1					
G4	3	3	3					



Table 5. Number of capacitive sensing channels available on STM32F098CC/RC/VC devices (continued)

Analog I/O group	Number of capacitive sensing channels						
Analog I/O group	STM32F098Vx	STM32F098Rx	STM32F098Cx				
G5	3	3	3				
G6	3	3	3				
G7	3	0	0				
G8	3	0	0				
Number of capacitive sensing channels	23	17	16				

## 3.14 Timers and watchdogs

The STM32F098CC/RC/VC devices include up to six general-purpose timers, two basic timers and an advanced control timer.

Table 6 compares the features of the different timers.

Table 6. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
Advanced control	TIM1	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	3
	TIM2 32-bit		Up, down, up/down	integer from 1 to 65536	Yes 4		-
	TIM3	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
General purpose	TIM14	16-bit	Up	integer from 1 to 65536	No	1	-
	TIM15 16-bit		Up	integer from 1 to 65536	Yes	2	1
	TIM16 TIM17	16-bit	Up	integer from 1 to 65536	Yes	1	1
Basic	TIM6 TIM7	16-bit	Up	integer from 1 to 65536	Yes	-	-

## 3.14.1 Advanced-control timer (TIM1)

The advanced-control timer (TIM1) can be seen as a three-phase PWM multiplexed on six channels. It has complementary PWM outputs with programmable inserted dead times. It

can also be seen as a complete general-purpose timer. The four independent channels can be used for:

- input capture
- output compare
- PWM generation (edge or center-aligned modes)
- one-pulse mode output

If configured as a standard 16-bit timer, it has the same features as the TIMx timer. If configured as the 16-bit PWM generator, it has full modulation capability (0-100%).

The counter can be frozen in debug mode.

Many features are shared with those of the standard timers which have the same architecture. The advanced control timer can therefore work together with the other timers via the Timer Link feature for synchronization or event chaining.

#### 3.14.2 General-purpose timers (TIM2, 3, 14, 15, 16, 17)

There are six synchronizable general-purpose timers embedded in the STM32F098CC/RC/VC devices (see *Table 6* for differences). Each general-purpose timer can be used to generate PWM outputs, or as simple time base.

#### TIM2, TIM3

STM32F098CC/RC/VC devices feature two synchronizable 4-channel general-purpose timers. TIM2 is based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. TIM3 is based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They feature 4 independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 12 input captures/output compares/PWMs on the largest packages.

The TIM2 and TIM3 general-purpose timers can work together or with the TIM1 advanced-control timer via the Timer Link feature for synchronization or event chaining.

TIM2 and TIM3 both have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Their counters can be frozen in debug mode.

#### **TIM14**

This timer is based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

TIM14 features one single channel for input capture/output compare, PWM or one-pulse mode output.

Its counter can be frozen in debug mode.

#### TIM15, TIM16 and TIM17

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

TIM15 has two independent channels, whereas TIM16 and TIM17 feature one single channel for input capture/output compare, PWM or one-pulse mode output.

The TIM15, TIM16 and TIM17 timers can work together, and TIM15 can also operate with TIM1 via the Timer Link feature for synchronization or event chaining.



TIM15 can be synchronized with TIM16 and TIM17.

TIM15, TIM16 and TIM17 have a complementary output with dead-time generation and independent DMA request generation.

Their counters can be frozen in debug mode.

#### 3.14.3 Basic timersTIM6 and TIM7

These timers are mainly used for DAC trigger generation. They can also be used as generic 16-bit time bases.

#### 3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on an 8-bit prescaler and 12-bit downcounter with user-defined refresh window. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop mode. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

#### 3.14.5 System window watchdog (WWDG)

The system window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the APB clock (PCLK). It has an early warning interrupt capability and the counter can be frozen in debug mode.

#### 3.14.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- a 24-bit down counter
- autoreload capability
- maskable system interrupt generation when the counter reaches 0
- programmable clock source (HCLK or HCLK/8)

## 3.15 Real-time clock (RTC) and backup registers

The RTC and the five backup registers are supplied through a switch that takes power either on  $V_{DD}$  supply when present or through the  $V_{BAT}$  pin. The backup registers are five 32-bit registers used to store 20 bytes of user application data when  $V_{DD}$  power is not present. They are not reset by a system or power reset.

The RTC is an independent BCD timer/counter. Its main features are the following:

- calendar with subseconds, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- automatic correction for 28, 29 (leap year), 30, and 31 day of the month
- programmable alarm with wake up from Stop mode capability
- Periodic wakeup unit with programmable resolution and period.
- on-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize the RTC with a master clock
- digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- Three anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop mode on tamper event detection
- timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop mode on timestamp event detection
- reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision

The RTC clock sources can be:

- a 32.768 kHz external crystal
- a resonator or oscillator
- the internal low-power RC oscillator (typical frequency of 40 kHz)
- the high-speed external clock divided by 32

## 3.16 Inter-integrated circuit interface (I<sup>2</sup>C)

Up to two I<sup>2</sup>C interfaces (I2C1 and I2C2) can operate in multimaster or slave modes. Both can support Standard mode (up to 100 kbit/s), Fast mode (up to 400 kbit/s) and Fast Mode Plus (up to 1 Mbit/s) with extra output drive on most of the associated I/Os.

Both support 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (two addresses, one with configurable mask). They also include programmable analog and digital noise filters.

Table 7. Comparison of I<sup>2</sup>C analog and digital filters

Aspect	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2Cx peripheral clocks
Benefits	Available in Stop mode	<ul><li>Extra filtering capability vs.</li><li>standard requirements</li><li>Stable length</li></ul>
Drawbacks	Variations depending on temperature, voltage, process	Wakeup from Stop on address match is not available when digital filter is enabled.

In addition, I2C1 provides hardware support for SMBUS 2.0 and PMBUS 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts



verifications and ALERT protocol management. I2C1 also has a clock domain independent from the CPU clock, allowing the I2C1 to wake up the MCU from Stop mode on address match.

The I2C peripherals can be served by the DMA controller.

Refer to Table 8 for the differences between I2C1 and I2C2.

Table 8. STM32F098CC/RC/VC I<sup>2</sup>C implementation

I <sup>2</sup> C features <sup>(1)</sup>	I2C1	I2C2
7-bit addressing mode	X	Х
10-bit addressing mode	Х	Х
Standard mode (up to 100 kbit/s)	Х	Х
Fast mode (up to 400 kbit/s)	Х	Х
Fast Mode Plus (up to 1 Mbit/s) with extra output drive I/Os	Х	Х
Independent clock	Х	-
SMBus	Х	-
Wakeup from STOP	Х	-

<sup>1.</sup> X = supported.

# 3.17 Universal synchronous/asynchronous receiver/transmitter (USART)

The device embeds up to eight universal synchronous/asynchronous receivers/transmitters (USART1, USART2, USART3, USART4, USART5, USART6, USART7, USART8) which communicate at speeds of up to 6 Mbit/s.

They provide hardware management of the CTS, RTS and RS485 DE signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. USART1, USART2 and USART3 support also SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability and auto baud rate feature, and have a clock domain independent of the CPU clock, allowing to wake up the MCU from Stop mode.

The USART interfaces can be served by the DMA controller.

Table 9. STM32F098CC/RC/VC USART implementation

USART modes/features <sup>(1)</sup>	USART1 USART2 USART3	USART4	USART5 USART6 USART7 USART8
Hardware flow control for modem	Х	Х	-
Continuous communication using DMA	Х	Х	Х
Multiprocessor communication	Х	Х	Х
Synchronous mode	Х	Х	Х
Smartcard mode	Х	-	-



USART modes/features <sup>(1)</sup>	USART1 USART2 USART3	USART4	USART5 USART6 USART7 USART8
Single-wire half-duplex communication	Х	Х	Х
IrDA SIR ENDEC block	Х	-	-
LIN mode	Х	-	-
Dual clock domain and wakeup from Stop mode	Х	-	-
Receiver timeout interrupt	Х	-	-
Modbus communication	Х	-	-
Auto baud rate detection	Х	-	-
Driver Enable	Х	Х	Х

Table 9. STM32F098CC/RC/VC USART implementation (continued)

# 3.18 Serial peripheral interface (SPI) / Inter-integrated sound interface (I<sup>2</sup>S)

Two SPIs are able to communicate up to 18 Mbit/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits.

Two standard I<sup>2</sup>S interfaces (multiplexed with SPI1 and SPI2 respectively) supporting four different audio standards can operate as master or slave at half-duplex communication mode. They can be configured to transfer 16 and 24 or 32 bits with 16-bit or 32-bit data resolution and synchronized by a specific signal. Audio sampling frequency from 8 kHz up to 192 kHz can be set by an 8-bit programmable linear prescaler. When operating in master mode, they can output a clock for an external audio component at 256 times the sampling frequency.

Table 10. STM32F098CC/RC/VC SPI/I<sup>2</sup>S implementation

SPI features <sup>(1)</sup>	SPI1 and SPI2
Hardware CRC calculation	X
Rx/Tx FIFO	X
NSS pulse mode	X
I <sup>2</sup> S mode	X
TI mode	X

<sup>1.</sup> X = supported.

<sup>1.</sup> X = supported.

# 3.19 High-definition multimedia interface (HDMI) - consumer electronics control (CEC)

The device embeds a HDMI-CEC controller that provides hardware support for the Consumer Electronics Control (CEC) protocol (Supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory overhead. It has a clock domain independent from the CPU clock, allowing the HDMI\_CEC controller to wakeup the MCU from Stop mode on data reception.

## 3.20 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

## 3.21 Clock recovery system (CRS)

The STM32F098CC/RC/VC embeds a special block which allows automatic trimming of the internal 48 MHz oscillator to guarantee its optimal accuracy over the whole device operational range. This automatic trimming is based on the external synchronization signal, which could be either derived from LSE oscillator, from an external signal on CRS\_SYNC pin or generated by user software. For faster lock-in during startup it is also possible to combine automatic trimming with manual trimming action.

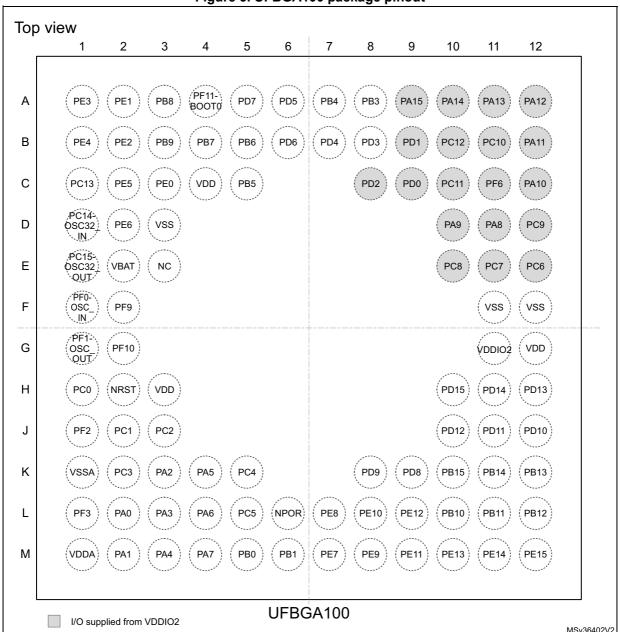
## 3.22 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.



## 4 Pinouts and pin descriptions

Figure 3. UFBGA100 package pinout



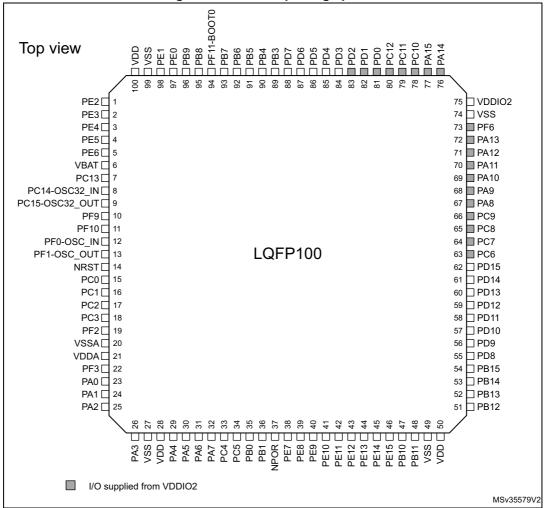


Figure 4. LQFP100 package pinout



Top view 1 2 3 5 7 8 6 0 PC14-OSC32 IN (PC13 PB9 PB4 PB3 (PA15) PA14 PA13 Α PC15-OSC32 PF11-BOOT0 PC10 PA12 В VBAT PB8 PD2 PC11 PF0-OSC\_ IN С VSS PB7 PB5 PC12 PA10 PA9 PA11 PF1-\ OSC\_ OUT D PB6 VDD VSS VSS VSS PA8 PC9 Ε (NRST) PC1 PC0 VDD VDD VDDIO2 PC7 PC8 F VSSA PC2 PA2 PA5 PB0 PC6 PB15 PB14 G PC3 PA0 PA3 PA6 PB1 (NPOR PB10 PB13 Н VDDA PA1 PA4 PA7 PC4 PC5 PB11 PB12 UFBGA64 I/O supplied from VDDIO2 MSv35569V2

Figure 5. UFBGA64 package pinout

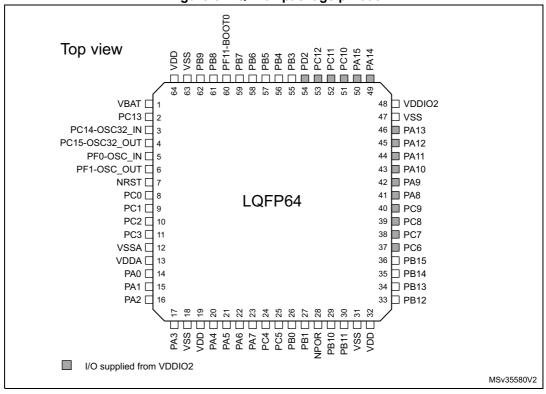


Figure 6. LQFP64 package pinout

Top view 1 2 3 4 5 6 7 8 Α VDDIO2 PA15 PC10 PD2 PB6 PB8 VSS VDD В PA12 VSS PA14 PC12 PB7 PB9 PC13 **VBAT** PC14-PC15-/PF11-OSC32 OSC32 С PA9 PA10 PA13 PC11 PB5 BOOT0 PF0-D OSC\_ IN PC7 PA8 PA11 PB3 PB4 PC2 NRST PF1-OSC\_ OUT Ε PC6 PC8 PC9 PA7 PA2 PC3 PC0 F PB15 PB13 PB1 PC5 PA5 PA1 PA0 PC1 G PB14 PB12 PB10 PB0 PA6 VDD VSS VSSA Н VDD VSS PB11 NPOR PC4 PA4 PA3 VDDA WLCSP64 I/O supplied from VDDIO2 MSv36405V3

Figure 7. WLCSP64 package pinout

The above figure shows the package in top view, changing from bottom view in the previous document versions.

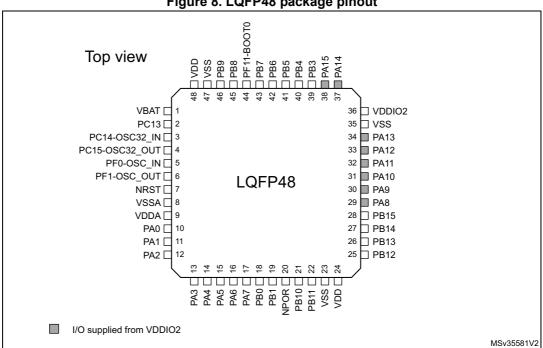


Figure 8. LQFP48 package pinout

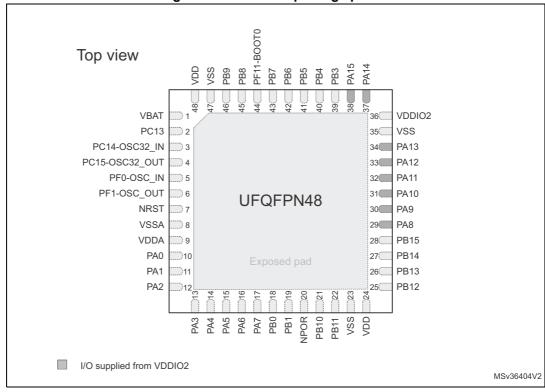


Figure 9. UFQFPN48 package pinout

Table 11. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition					
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name					
	S	Supply pin					
Pin type	I	Input-only pin					
	I/O	Input / output pin					
	FT	5 V-tolerant I/O					
	FTf	5 V-tolerant I/O, FM+ capable					
	TTa	3.3 V-tolerant I/O directly connected to ADC					
I/O structure	POR	External power on reset pin with embedded weak pull-up resistor, powered from $V_{\rm DDA}$					
	TC	Standard 3.3 V I/O					
	В	Dedicated BOOT0 pin					
	RST Bidirectional reset pin with embedded weak pull-up resisto						
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.						

Table 11. Legend/abbreviations used in the pinout table (continued)

Na	me	Abbreviation	Definition			
Pin	Alternate functions	Leunctions selected through GPIOx AER registers				
functions	Additional functions	Functions directly	selected/enabled through peripheral registers			

Table 12. STM32F098CC/RC/VC pin definitions

	Pi	n nui	mber	s						Pin functions		
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions	
B2	1	-	-	-	-	PE2	I/O	FT		TSC_G7_IO1, TIM3_ETR	-	
A1	2	-	-	-	-	PE3	I/O	FT		TSC_G7_IO2, TIM3_CH1	-	
B1	3	-	-	-	-	PE4	I/O	FT		TSC_G7_IO3, TIM3_CH2	-	
C2	4	-	-	-	-	PE5	I/O	FT		TSC_G7_IO4, TIM3_CH3	-	
D2	5	-	-	-	-	PE6	I/O	FT		TIM3_CH4	WKUP3, RTC_TAMP3	
E2	6	B2	1	В8	1	VBAT	S	-	-	Backup power s	upply	
C1	7	A2	2	В7	2	PC13	I/O	TC	(1) (2)	-	WKUP2, RTC_TAMP1, RTC_TS, RTC_OUT	
D1	8	A1	3	C8	3	PC14- OSC32_IN (PC14)	I/O	TC	(1) (2)	-	OSC32_IN	
E1	9	B1	4	C7	4	PC15- OSC32_OUT (PC15)	I/O	TC	(1) (2)	-	OSC32_OUT	
F2	10	-	-	-	-	PF9	I/O	FT		TIM15_CH1, USART6_TX	-	
G2	11	-	-	-	-	PF10	I/O	FT		TIM15_CH2, USART6_RX	-	
F1	12	C1	5	D8	5	PF0-OSC_IN (PF0)	I/O	FTf		CRS_SYNC, I2C1_SDA	OSC_IN	
G1	13	D1	6	E8	6	PF1-OSC_OUT (PF1)	I/O	FTf		I2C1_SCL	OSC_OUT	
H2	14	E1	7	D7	7	NRST	I/O	RST		Device reset input / internal reset output (active low)		

Table 12. STM32F098CC/RC/VC pin definitions (continued)

	Pi	n nui	nber	s						Pin functions		
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions	
H1	15	E3	8	E7	1	PC0	I/O	TTa		EVENTOUT, USART6_TX, USART7_TX	ADC_IN10	
J2	16	E2	9	F8	ı	PC1	I/O	ТТа		EVENTOUT, USART6_RX, USART7_RX	ADC_IN11	
J3	17	F2	10	D6	ı	PC2	I/O	TTa		SPI2_MISO, I2S2_MCK, EVENTOUT, USART8_TX	ADC_IN12	
K2	18	G1	11	E6	į	PC3	I/O	TTa		SPI2_MOSI, I2S2_SD, EVENTOUT, USART8_RX	ADC_IN13	
J1	19	ı	ı	1	ı	PF2	I/O	FT		EVENTOUT, USART7_TX, USART7_CK_RTS	WKUP8	
K1	20	F1	12	G8	8	VSSA	S	-		Analog ground		
M1	21	H1	13	Н8	9	VDDA	S	-		Analog power s	upply	
L1	22	1	-	-	1	PF3	I/O	FT		EVENTOUT, USART7_RX, USART6_CK_RTS		
L2	23	G2	14	F7	10	PA0	I/O	ТТа		USART2_CTS, TIM2_CH1_ETR, TSC_G1_IO1, USART4_TX COMP1_OUT	RTC_TAMP2, WKUP1, ADC_IN0, COMP1_INM6	
M2	24	H2	15	F6	11	PA1	I/O	ТТа		USART2_RTS, TIM2_CH2, TIM15_CH1N, TSC_G1_IO2, USART4_RX, EVENTOUT	ADC_IN1, COMP1_INP	
K3	25	F3	16	E5	12	PA2	I/O	TTa		USART2_TX, TIM2_CH3, TIM15_CH1, TSC_G1_IO3 COMP2_OUT	ADC_IN2, WKUP4, COMP2_INM6	
L3	26	G3	17	Н7	13	PA3	I/O	TTa		USART2_RX,TIM2_CH4, TIM15_CH2, TSC_G1_IO4	ADC_IN3, COMP2_INP	
D3	27	C2	18	G7	-	VSS	S	-		Ground		



Table 12. STM32F098CC/RC/VC pin definitions (continued)

Pin numbers										Pin functions	
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
НЗ	28	D2	19	G6	-	VDD	S	-		Digital power supply	
М3	29	НЗ	20	Н6	14	PA4	I/O	ТТа		SPI1_NSS, I2S1_WS, TIM14_CH1, TSC_G2_IO1, USART2_CK, USART6_TX	COMP1_INM4, COMP2_INM4, ADC_IN4, DAC_OUT1
K4	30	F4	21	F5	15	PA5	I/O	ТТа		SPI1_SCK, I2S1_CK, CEC, TIM2_CH1_ETR, TSC_G2_IO2, USART6_RX	COMP1_INM5, COMP2_INM5, ADC_IN5, DAC_OUT2
L4	31	G4	22	G5	16	PA6	I/O	ТТа		SPI1_MISO, I2S1_MCK, TIM3_CH1, TIM1_BKIN, TIM16_CH1, COMP1_OUT, TSC_G2_IO3, EVENTOUT, USART3_CTS	ADC_IN6
M4	32	H4	23	E4	17	PA7	I/O	ТТа		SPI1_MOSI, I2S1_SD, TIM3_CH2, TIM14_CH1, TIM1_CH1N, TIM17_CH1, COMP2_OUT, TSC_G2_IO4, EVENTOUT	ADC_IN7
K5	33	H5	24	H5	-	PC4	I/O	TTa		EVENTOUT, USART3_TX	ADC_IN14
L5	34	H6	25	F4	-	PC5	I/O	TTa		TSC_G3_IO1, USART3_RX	ADC_IN15, WKUP5
M5	35	F5	26	G4	18	PB0	I/O	ТТа		TIM3_CH3, TIM1_CH2N, TSC_G3_IO2, EVENTOUT, USART3_CK	ADC_IN8
M6	36	G5	27	F3	19	PB1	I/O	ТТа		TIM3_CH4, USART3_RTS, TIM14_CH1, TIM1_CH3N, TSC_G3_IO3	ADC_IN9
L6	37	G6	28	H4	20	NPOR	I	POR	(3)	Device power-on reset input (active low)	
M7	38	-	-	-	-	PE7	I/O	FT		TIM1_ETR, USART5_CK_RTS	-

Table 12. STM32F098CC/RC/VC pin definitions (continued)

	Pi	in nuı	mber							Pin function	ıs
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
L7	39	-	-	-	-	PE8	I/O	FT		TIM1_CH1N, USART4_TX	-
M8	40	-	-	-	ı	PE9	I/O	FT		TIM1_CH1, USART4_RX	-
L8	41	-	-	-	1	PE10	I/O	FT		TIM1_CH2N, USART5_TX	-
М9	42	-	-	-	-	PE11	I/O	FT		TIM1_CH2, USART5_RX	-
L9	43	-	-	-	-	PE12	I/O	FT		SPI1_NSS, I2S1_WS, TIM1_CH3N	-
M10	44	-	-	-	-	PE13	I/O	FT		SPI1_SCK, I2S1_CK, TIM1_CH3	-
M11	45	-	-	-	-	PE14	I/O	FT		SPI1_MISO, I2S1_MCK, TIM1_CH4	-
M12	46	-	-	-	-	PE15	I/O	FT		SPI1_MOSI, I2S1_SD, TIM1_BKIN	-
L10	47	G7	29	G3	21	PB10	I/O	FTf		SPI2_SCK, I2S2_CK, I2C2_SCL, USART3_TX, CEC, TSC_SYNC, TIM2_CH3	-
L11	48	H7	30	НЗ	22	PB11	I/O	FTf		USART3_RX, TIM2_CH4, EVENTOUT, TSC_G6_IO1, I2C2_SDA	-
F12	49	D5	31	H2	23	VSS	S	ı		Ground	
G12	50	E5	32	H1	24	VDD	S	İ		Digital power su	apply
L12	51	Н8	33	G2	25	PB12	I/O	FT		TIM1_BKIN, TIM15_BKIN, SPI2_NSS, I2S2_WS, USART3_CK, TSC_G6_IO2, EVENTOUT	-
K12	52	G8	34	F2	26	PB13	I/O	FTf		SPI2_SCK, I2S2_CK, I2C2_SCL, USART3_CTS, TIM1_CH1N, TSC_G6_IO3	-



Table 12. STM32F098CC/RC/VC pin definitions (continued)

	Pi	n nui	mber	s						Pin function	ıs
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
K11	53	F8	35	G1	27	PB14	I/O	FTf		SPI2_MISO, I2S2_MCK, I2C2_SDA, USART3_RTS, TIM1_CH2N, TIM15_CH1, TSC_G6_IO4	-
K10	54	F7	36	F1	28	PB15	I/O	FT		SPI2_MOSI, I2S2_SD, TIM1_CH3N, TIM15_CH1N, TIM15_CH2	WKUP7, RTC_REFIN
K9	55	-	-	-	-	PD8	I/O	FT		USART3_TX	-
K8	56	-	-	-	-	PD9	I/O	FT		USART3_RX	-
J12	57	-	-	-	-	PD10	I/O	FT		USART3_CK	-
J11	58	-	-	-	-	PD11	I/O	FT		USART3_CTS	-
J10	59	-	-	-	-	PD12	I/O	FT		USART3_RTS, TSC_G8_IO1, USART8_CK_RTS	-
H12	60	1	1	-	-	PD13	I/O	FT		TSC_G8_IO2, USART8_TX	-
H11	61	ı	ı	-	-	PD14	I/O	FT		TSC_G8_IO3, USART8_RX	-
H10	62	-	-	-	-	PD15	I/O	FT		TSC_G8_IO4, CRS_SYNC, USART7_CK_RTS	-
E12	63	F6	37	E1	-	PC6	I/O	FT	(4)	TIM3_CH1, USART7_TX	-
E11	64	E7	38	D1	-	PC7	I/O	FT	(4)	TIM3_CH2, USART7_RX	-
E10	65	E8	39	E2	-	PC8	I/O	FT	(4)	TIM3_CH3, USART8_TX	-
D12	66	D8	40	E3	-	PC9	I/O	FT	(4)	TIM3_CH4, USART8_RX	-
D11	67	D7	41	D2	29	PA8	I/O	FT	(4)	USART1_CK, TIM1_CH1, EVENTOUT, MCO, CRS_SYNC	-
D10	68	C7	42	C1	30	PA9	I/O	FT	(4)	USART1_TX, TIM1_CH2, TIM15_BKIN, MCO, TSC_G4_IO1, I2C1_SCL	-
C12	69	C6	43	C2	31	PA10	I/O	FT	(4)	USART1_RX, TIM1_CH3, TIM17_BKIN, TSC_G4_IO2, I2C1_SDA	-

Table 12. STM32F098CC/RC/VC pin definitions (continued)

	Pi	n nui	mber	s						Pin function	ıs
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
B12	70	C8	44	D3	32	PA11	I/O	FT	(4)	CAN_RX, USART1_CTS, TIM1_CH4, COMP1_OUT, TSC_G4_IO3, EVENTOUT, I2C2_SCL	-
A12	71	B8	45	B1	33	PA12	I/O	FT	(4)	CAN_TX, USART1_RTS, TIM1_ETR, COMP2_OUT, TSC_G4_IO4, EVENTOUT, I2C2_SDA	-
A11	72	A8	46	С3	34	PA13	I/O	FT	(4) (5)	IR_OUT, SWDIO	-
C11	73	-	-	-	-	PF6	I/O	FT	(4)	-	-
F11	74	D6	47	B2	35	VSS	S	-		Ground	
G11	75	E6	48	A1	36	VDDIO2	S	-		Digital power supply	
A10	76	A7	49	В3	37	PA14	I/O	FT	(4) (5)	USART2_TX, SWCLK	-
A9	77	A6	50	A2	38	PA15	I/O	FT	(4)	SPI1_NSS, I2S1_WS, USART2_RX, USART4_RTS, TIM2_CH1_ETR, EVENTOUT	-
B11	78	В7	51	А3	-	PC10	I/O	FT	(4)	USART3_TX, USART4_TX	-
C10	79	В6	52	C4	-	PC11	I/O	FT	(4)	USART3_RX, USART4_RX	-
B10	80	C5	53	B4	-	PC12	I/O	FT	(4)	USART3_CK, USART4_CK, USART5_TX	-
C9	81	-	-	-	-	PD0	I/O	FT	(4)	SPI2_NSS, I2S2_WS, CAN_RX	-
В9	82	-	-	-	-	PD1	I/O	FT	(4)	SPI2_SCK, I2S2_CK CAN_TX	-
C8	83	B5	54	A4	-	PD2	I/O	FT	(4)	USART3_RTS, TIM3_ETR, USART5_RX	-
В8	84	-	-	-	-	PD3	I/O	FT		SPI2_MISO, I2S2_MCK, USART2_CTS	-



Table 12. STM32F098CC/RC/VC pin definitions (continued)

	Pi	n nui	nber							Pin function	ıs
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
В7	85	ı	-	-	-	PD4	I/O	FT		SPI2_MOSI, I2S2_SD, USART2_RTS	-
A6	86	-	-	-	-	PD5	I/O	FT		USART2_TX	-
В6	87	ı	-	-	-	PD6	I/O	FT		USART2_RX	-
A5	88	ı	-	-	-	PD7	I/O	FT		USART2_CK	-
A8	89	A5	55	D4	39	PB3	I/O	FT		SPI1_SCK, I2S1_CK, TIM2_CH2, TSC_G5_IO1, EVENTOUT, USART5_TX	-
A7	90	A4	56	D5	40	PB4	I/O	FT		SPI1_MISO, I2S1_MCK, TIM17_BKIN, TIM3_CH1, TSC_G5_IO2, EVENTOUT, USART5_RX	-
C5	91	C4	57	C5	41	PB5	I/O	FT		SPI1_MOSI, I2S1_SD, I2C1_SMBA, TIM16_BKIN, TIM3_CH2, USART5_CK_RTS	WKUP6
B5	92	D3	58	A5	42	PB6	I/O	FTf		I2C1_SCL, USART1_TX, TIM16_CH1N, TSC_G5_I03	-
B4	93	С3	59	B5	43	PB7	1/0	FTf		I2C1_SDA, USART1_RX, USART4_CTS, TIM17_CH1N, TSC_G5_IO4	-
A4	94	B4	60	C6	44	PF11-BOOT0	I/O	FT		-	Boot memory selection
A3	95	ВЗ	61	A6	45	PB8	I/O	FTf		I2C1_SCL, CEC, TIM16_CH1, TSC_SYNC, CAN_RX	-
В3	96	A3	62	В6	46	PB9	I/O	FTf		SPI2_NSS, I2S2_WS, I2C1_SDA, IR_OUT, TIM17_CH1, EVENTOUT, CAN_TX	-
С3	97	-	ı	_	-	PE0	I/O	FT		EVENTOUT, TIM16_CH1	-
A2	98	ı	-	-	-	PE1	I/O	FT		EVENTOUT, TIM17_CH1	-



Pin numbers Pin functions LQFP48/UFQFPN48 //O structure Pin type Pin name Notes UFBGA100 **UFBGA64** WLCSP64 LQFP100 LQFP64 (function upon **Additional Alternate functions** reset) **functions VSS** S D3 99 D4 63 Α7 47 Ground 100 **A8** 48 VDD S C4 E4 64 Digital power supply

Table 12. STM32F098CC/RC/VC pin definitions (continued)



PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:

- The speed should not exceed 2 MHz with a maximum load of 30 pF.

- These GPIOs must not be used as current sources (e.g. to drive an LED).

<sup>2.</sup> After the first RTC domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers which are not reset by the system reset. For details on how to manage these GPIOs, refer to the RTC domain and RTC register descriptions in the reference manual.

<sup>3.</sup> This pin is powered by VDDA.

<sup>4.</sup> PC6, PC7, PC8, PC9, PA8, PA9, PA10, PA11, PA12, PA13, PF6, PA14, PA15, PC10, PC11, PC12, PD0, PD1 and PD2 I/Os are supplied by VDDIO2

<sup>5.</sup> After reset, these pins are configured as SWDIO and SWCLK alternate functions, and the internal pull-up on the SWDIO pin and the internal pull-down on the SWCLK pin are activated.



Table 13. Alternate functions selected through GPIOA\_AFR registers for port A

Pin name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PA0	-	USART2_CTS	TIM2_CH1_ETR	TSC_G1_IO1	USART4_TX	-	-	COMP1_OUT
PA1	EVENTOUT	USART2_RTS	TIM2_CH2	TSC_G1_IO2	USART4_RX	TIM15_CH1N	-	-
PA2	TIM15_CH1	USART2_TX	TIM2_CH3	TSC_G1_IO3	-	-	-	COMP2_OUT
PA3	TIM15_CH2	USART2_RX	TIM2_CH4	TSC_G1_IO4	-	-	-	-
PA4	SPI1_NSS, I2S1_WS	USART2_CK	-	TSC_G2_IO1	TIM14_CH1	USART6_TX	-	-
PA5	SPI1_SCK, I2S1_CK	CEC	TIM2_CH1_ETR	TSC_G2_IO2	-	USART6_RX	-	-
PA6	SPI1_MISO, I2S1_MCK	TIM3_CH1	TIM1_BKIN	TSC_G2_IO3	USART3_CTS	TIM16_CH1	EVENTOUT	COMP1_OUT
PA7	SPI1_MOSI, I2S1_SD	TIM3_CH2	TIM1_CH1N	TSC_G2_IO4	TIM14_CH1	TIM17_CH1	EVENTOUT	COMP2_OUT
PA8	MCO	USART1_CK	TIM1_CH1	EVENTOUT	CRS_SYNC	-	-	-
PA9	TIM15_BKIN	USART1_TX	TIM1_CH2	TSC_G4_IO1	I2C1_SCL	MCO	-	-
PA10	TIM17_BKIN	USART1_RX	TIM1_CH3	TSC_G4_IO2	I2C1_SDA	-	-	-
PA11	EVENTOUT	USART1_CTS	TIM1_CH4	TSC_G4_IO3	CAN_RX	I2C2_SCL	-	COMP1_OUT
PA12	EVENTOUT	USART1_RTS	TIM1_ETR	TSC_G4_IO4	CAN_TX	I2C2_SDA	-	COMP2_OUT
PA13	SWDIO	IR_OUT	-	-	-	-	-	-
PA14	SWCLK	USART2_TX	-	-	-	-	-	-
PA15	SPI1_NSS, I2S1_WS	USART2_RX	TIM2_CH1_ETR	EVENTOUT	USART4_RTS	-	-	-

Table 14	. Alternate funct	ions selected thro	ugh GPIOB_AFR	registers for port B

Pin name	AF0	AF1	AF2	AF3	AF4	AF5
PB0	EVENTOUT	TIM3_CH3	TIM1_CH2N	TSC_G3_IO2	USART3_CK	-
PB1	TIM14_CH1	TIM3_CH4	TIM1_CH3N	TSC_G3_IO3	USART3_RTS	-
PB3	SPI1_SCK, I2S1_CK	EVENTOUT	TIM2_CH2	TSC_G5_IO1		-
PB4	SPI1_MISO, I2S1_MCK	TIM3_CH1	EVENTOUT	TSC_G5_IO2		TIM17_BKIN
PB5	SPI1_MOSI, I2S1_SD	TIM3_CH2	TIM16_BKIN	I2C1_SMBA		-
PB6	USART1_TX	I2C1_SCL	TIM16_CH1N	TSC_G5_IO3	-	-
PB7	USART1_RX	I2C1_SDA	TIM17_CH1N	TSC_G5_IO4	USART4_CTS	-
PB8	CEC	I2C1_SCL	TIM16_CH1	TSC_SYNC	CAN_RX	-
PB9	IR_OUT	I2C1_SDA	TIM17_CH1	EVENTOUT	CAN_TX	SPI2_NSS, I2S2_WS
PB10	CEC	I2C2_SCL	TIM2_CH3	TSC_SYNC	USART3_TX	SPI2_SCK, I2S2_CK
PB11	EVENTOUT	I2C2_SDA	TIM2_CH4	TSC_G6_IO1	USART3_RX	-
PB12	SPI2_NSS, I2S2_WS	EVENTOUT	TIM1_BKIN	TSC_G6_IO2	USART3_CK	TIM15_BKIN
PB13	SPI2_SCK, I2S2_CK	-	TIM1_CH1N	TSC_G6_IO3	USART3_CTS	I2C2_SCL
PB14	SPI2_MISO, I2S2_MCK	TIM15_CH1	TIM1_CH2N	TSC_G6_IO4	USART3_RTS	I2C2_SDA
PB15	SPI2_MOSI, I2S2_SD	TIM15_CH2	TIM1_CH3N	TIM15_CH1N	-	-

Table 15. Alternate functions selected through GPIOC\_AFR registers for port C

Pin name	AF0	AF1	AF2
PC0	EVENTOUT	USART7_TX	USART6_TX
PC1	EVENTOUT	USART7_RX	USART6_RX
PC2	EVENTOUT	SPI2_MISO, I2S2_MCK	USART8_TX
PC3	EVENTOUT	SPI2_MOSI, I2S2_SD	USART8_RX
PC4	EVENTOUT	USART3_TX	-
PC5	TSC_G3_IO1	USART3_RX	-
PC6	TIM3_CH1	USART7_TX	-
PC7	TIM3_CH2	USART7_RX	-
PC8	TIM3_CH3	USART8_TX	-
PC9	TIM3_CH4	USART8_RX	-
PC10	USART4_TX	USART3_TX	-
PC11	USART4_RX	USART3_RX	-
PC12	USART4_CK	USART3_CK	USART5_TX
PC13	-	-	-
PC14	-	-	-
PC15	-	-	-

Table 16. Alternate functions selected through GPIOD\_AFR registers for port D

Pin name	AF0	AF1	AF2
PD0	CAN_RX	SPI2_NSS, I2S2_WS	-
PD1	CAN_TX	SPI2_SCK, I2S2_CK	-
PD2	TIM3_ETR	USART3_RTS	USART5_RX
PD3	USART2_CTS	SPI2_MISO, I2S2_MCK	-
PD4	USART2_RTS	SPI2_MOSI, I2S2_SD	-
PD5	USART2_TX	-	-
PD6	USART2_RX	-	-
PD7	USART2_CK	-	-
PD8	USART3_TX	-	-
PD9	USART3_RX	-	-
PD10	USART3_CK	-	-
PD11	USART3_CTS	-	-
PD12	USART3_RTS	TSC_G8_IO1	USART8_CK_RTS
PD13	USART8_TX	TSC_G8_IO2	-
PD14	USART8_RX	TSC_G8_IO3	-
PD15	CRS_SYNC	TSC_G8_IO4	USART7_CK_RTS



Table 17. Alternate functions selected through GPIOE\_AFR registers for port E

Pin name	AF0	AF1
PE0	TIM16_CH1	EVENTOUT
PE1	TIM17_CH1	EVENTOUT
PE2	TIM3_ETR	TSC_G7_IO1
PE3	TIM3_CH1	TSC_G7_IO2
PE4	TIM3_CH2	TSC_G7_IO3
PE5	TIM3_CH3	TSC_G7_IO4
PE6	TIM3_CH4	-
PE7	TIM1_ETR	USART5_CK_RTS
PE8	TIM1_CH1N	USART4_TX
PE9	TIM1_CH1	USART4_RX
PE10	TIM1_CH2N	USART5_TX
PE11	TIM1_CH2	USART5_RX
PE12	TIM1_CH3N	SPI1_NSS, I2S1_WS
PE13	TIM1_CH3	SPI1_SCK, I2S1_CK
PE14	TIM1_CH4	SPI1_MISO, I2S1_MCK
PE15	TIM1_BKIN	SPI1_MOSI, I2S1_SD

Table 18. Alternate functions selected through GPIOF\_AFR registers for port F

Pin name	AF0	AF1	AF2
PF0	CRS_SYNC	I2C1_SDA	-
PF1	-	I2C1_SCL	-
PF2	EVENTOUT	USART7_TX	USART7_CK_RTS
PF3	EVENTOUT	USART7_RX	USART6_CK_RTS
PF6	-	-	-
PF9	TIM15_CH1	USART6_TX	-
PF10	TIM15_CH2	USART6_RX	-

# 5 Memory mapping

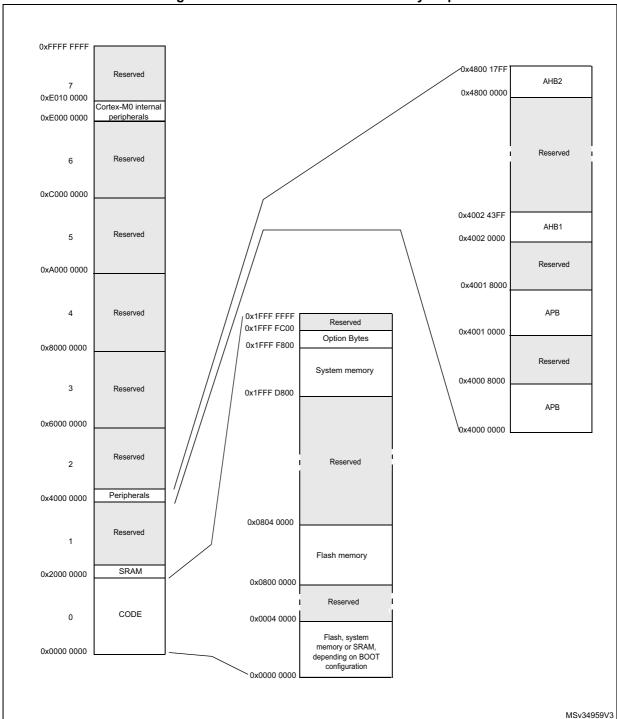


Figure 10. STM32F098CC/RC/VC memory map



Table 19. STM32F098CC/RC/VC peripheral register boundary addresses

Bus	Boundary address	Size	Peripheral
	0x4800 1800 - 0x5FFF FFFF	~384 MB	Reserved
	0x4800 1400 - 0x4800 17FF	1 KB	GPIOF
	0x4800 1000 - 0x4800 13FF	1 KB	GPIOE
AHB2	0x4800 0C00 - 0x4800 0FFF	1 KB	GPIOD
ALIDZ	0x4800 0800 - 0x4800 0BFF	1 KB	GPIOC
	0x4800 0400 - 0x4800 07FF	1 KB	GPIOB
	0x4800 0000 - 0x4800 03FF	1 KB	GPIOA
	0x4002 4400 - 0x47FF FFFF	~128 MB	Reserved
	0x4002 4000 - 0x4002 43FF	1 KB	TSC
	0x4002 3400 - 0x4002 3FFF	3 KB	Reserved
	0x4002 3000 - 0x4002 33FF	1 KB	CRC
	0x4002 2400 - 0x4002 2FFF	3 KB	Reserved
AHB1	0x4002 2000 - 0x4002 23FF	1 KB	Flash memory interface
	0x4002 1400 - 0x4002 1FFF	3 KB	Reserved
	0x4002 1000 - 0x4002 13FF	1 KB	RCC
	0x4002 0400 - 0x4002 0FFF	3 KB	Reserved
	0x4002 0000 - 0x4002 03FF	1 KB	DMA
	0x4001 8000 - 0x4001 FFFF	32 KB	Reserved

Table 19. STM32F098CC/RC/VC peripheral register boundary addresses (continued)

Bus	Boundary address	Size	Peripheral
	0x4001 5C00 - 0x4001 7FFF	9 KB	Reserved
	0x4001 5800 - 0x4001 5BFF	1 KB	DBGMCU
	0x4001 4C00 - 0x4001 57FF	3 KB	Reserved
	0x4001 4800 - 0x4001 4BFF	1 KB	TIM17
	0x4001 4400 - 0x4001 47FF	1 KB	TIM16
	0x4001 4000 - 0x4001 43FF	1 KB	TIM15
	0x4001 3C00 - 0x4001 3FFF	1 KB	Reserved
	0x4001 3800 - 0x4001 3BFF	1 KB	USART1
	0x4001 3400 - 0x4001 37FF	1 KB	Reserved
	0x4001 3000 - 0x4001 33FF	1 KB	SPI1/I2S1
APB	0x4001 2C00 - 0x4001 2FFF	1 KB	TIM1
	0x4001 2800 - 0x4001 2BFF	1 KB	Reserved
	0x4001 2400 - 0x4001 27FF	1 KB	ADC
	0x4001 2000 - 0x4001 23FF	1 KB	Reserved
	0x4001 1C00 – 0x4001 1FFF	1 KB	USART8
	0x4001 1800 – 0x4001 1BFF	1 KB	USART7
	0x4001 1400 – 0x4001 17FF	1 KB	USART6
	0x4001 0800 - 0x4001 13FF	3 KB	Reserved
	0x4001 0400 - 0x4001 07FF	1 KB	EXTI
	0x4001 0000 - 0x4001 03FF	1 KB	SYSCFG + COMP
	0x4000 8000 - 0x4000 FFFF	32 KB	Reserved

Table 19. STM32F098CC/RC/VC peripheral register boundary addresses (continued)

Bus	Boundary address	Size	Peripheral
	0x4000 7C00 - 0x4000 7FFF	1 KB	Reserved
	0x4000 7800 - 0x4000 7BFF	1 KB	CEC
	0x4000 7400 - 0x4000 77FF	1 KB	DAC
	0x4000 7000 - 0x4000 73FF	1 KB	PWR
	0x4000 6C00 - 0x4000 6FFF	1 KB	CRS
	0x4000 6800 - 0x4000 6BFF	1 KB	Reserved
	0x4000 6400 - 0x4000 67FF	1 KB	BxCAN
	0x4000 6100 - 0x4000 63FF	768 B	Reserved
	0x4000 6000 - 0x4000 60FF	256 B	CAN RAM
	0x4000 5C00 - 0x4000 5FFF	1 KB	Reserved
	0x4000 5800 - 0x4000 5BFF	1 KB	I2C2
	0x4000 5400 - 0x4000 57FF	1 KB	I2C1
	0x4000 5000 - 0x4000 53FF	1 KB	USART5
	0x4000 4C00 - 0x4000 4FFF	1 KB	USART4
	0x4000 4800 - 0x4000 4BFF	1 KB	USART3
	0x4000 4400 - 0x4000 47FF	1 KB	USART2
	0x4000 3C00 - 0x4000 43FF	2 KB	Reserved
APB	0x4000 3800 - 0x4000 3BFF	1 KB	SPI2
	0x4000 3400 - 0x4000 37FF	1 KB	Reserved
	0x4000 3000 - 0x4000 33FF	1 KB	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 KB	WWDG
	0x4000 2800 - 0x4000 2BFF	1 KB	RTC
	0x4000 2400 - 0x4000 27FF	1 KB	Reserved
	0x4000 2000 - 0x4000 23FF	1 KB	TIM14
	0x4000 1800 - 0x4000 1FFF	2 KB	Reserved
	0x4000 1400 - 0x4000 17FF	1 KB	TIM7
	0x4000 1000 - 0x4000 13FF	1 KB	TIM6
	0x4000 0800 - 0x4000 0FFF	2 KB	Reserved
	0x4000 0400 - 0x4000 07FF	1 KB	TIM3
	0x4000 0000 - 0x4000 03FF	1 KB	TIM2

## 6 Electrical characteristics

#### 6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V<sub>SS</sub>.

#### 6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at  $T_A = 25$  °C and  $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean ±3σ).

### 6.1.2 Typical values

Unless otherwise specified, typical data are based on  $T_A$  = 25 °C,  $V_{DD}$  = 1.8 V and  $V_{DDA}$  = 3.3 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean ±2σ).

## 6.1.3 Typical curves

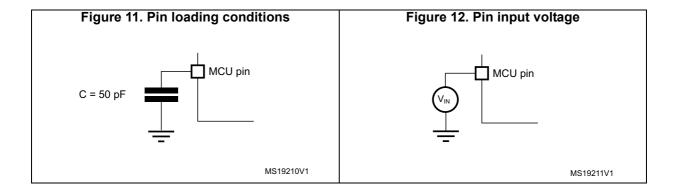
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

#### 6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 11*.

#### 6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in Figure 12.



5//

### 6.1.6 Power supply scheme

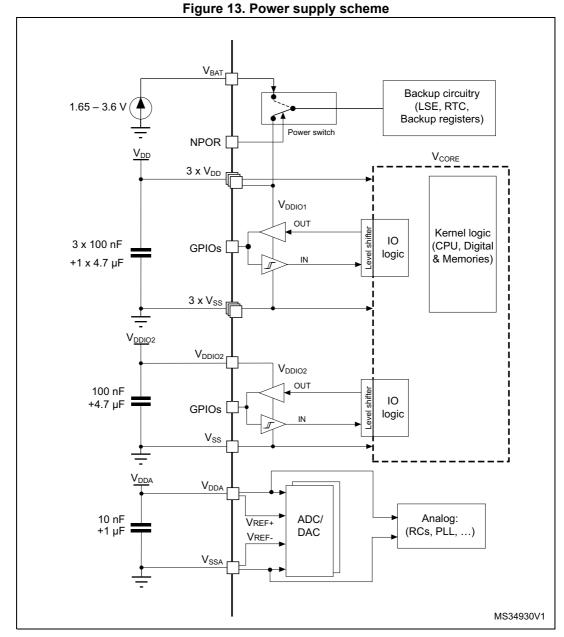


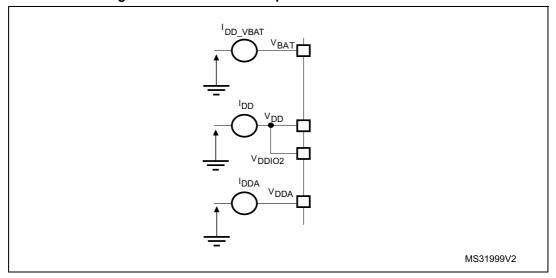
Figure 40 Davis and a sale of

Caution:

Each power supply pair ( $V_{DD}/V_{SS}$ ,  $V_{DDA}/V_{SSA}$  etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

## 6.1.7 Current consumption measurement

Figure 14. Current consumption measurement scheme



## 6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 20: Voltage characteristics*, *Table 21: Current characteristics* and *Table 22: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 20. Voltage characteristics<sup>(1)</sup>

Symbol	Ratings	Min	Max	Unit
V <sub>DD</sub> -V <sub>SS</sub>	External main supply voltage	-0.3	1.95	V
V <sub>DDIO2</sub> -V <sub>SS</sub>	External I/O supply voltage	-0.3	4.0	V
V <sub>DDA</sub> -V <sub>SS</sub>	External analog supply voltage	-0.3	4.0	V
V <sub>DD</sub> -V <sub>DDA</sub>	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	٧
V <sub>BAT</sub> -V <sub>SS</sub>	External backup supply voltage	-0.3	4.0	V
	Input voltage on FT and FTf pins	V <sub>SS</sub> -0.3	$V_{\rm DDIOx} + 4.0^{(3)}$	٧
V <sub>IN</sub> <sup>(2)</sup>	Input voltage on POR pins	V <sub>SS</sub> -0.3	4.0	V
VIN.	Input voltage on TTa pins	V <sub>SS</sub> -0.3	4.0	V
	Input voltage on any other pin	V <sub>SS</sub> -0.3	4.0	٧
ΔV <sub>DDx</sub>	Variations between different V <sub>DD</sub> power pins	-	50	mV
V <sub>SSx</sub> -V <sub>SS</sub>	Variations between all the different ground pins	-	50	mV
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	see Section 6.3 sensitivity chara		-

All main power (V<sub>DD</sub>, V<sub>DDA</sub>) and ground (V<sub>SS</sub>, V<sub>SSA</sub>) pins must always be connected to the external power supply, in the permitted range.

<sup>2.</sup> V<sub>IN</sub> maximum must always be respected. Refer to *Table 21: Current characteristics* for the maximum allowed injected current values.

<sup>3.</sup> Valid only if the internal pull-up/pull-down resistors are disabled. If internal pull-up or pull-down resistor is enabled, the maximum limit is 4 V.

**Table 21. Current characteristics** 

Symbol	Ratings	Max.	Unit
$\Sigma I_{VDD}$	Total current into sum of all VDD power lines (source) <sup>(1)</sup>	120	
Σl <sub>VSS</sub>	Total current out of sum of all VSS ground lines (sink) <sup>(1)</sup>	-120	
I <sub>VDD(PIN)</sub>	Maximum current into each VDD power pin (source) <sup>(1)</sup>	100	
I <sub>VSS(PIN)</sub>	Maximum current out of each VSS ground pin (sink) <sup>(1)</sup>	-100	
,	Output current sunk by any I/O and control pin	25	
I <sub>IO(PIN)</sub>	Output current source by any I/O and control pin	-25	
	Total output current sunk by sum of all I/Os and control pins <sup>(2)</sup>	80	
$\Sigma I_{IO(PIN)}$	Total output current sourced by sum of all I/Os and control pins <sup>(2)</sup>	-80	mA
	Total output current sourced by sum of all I/Os supplied by VDDIO2	-40	
	Injected current on POR, FT and FTf pins	-5/+0 <sup>(4)</sup>	
$I_{\rm INJ(PIN)}^{(3)}$	Injected current on TC and RST pin	± 5	
	Injected current on TTa pins <sup>(5)</sup>	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins) <sup>(6)</sup>	± 25	

- 1. All main power (VDD, VDDA) and ground (VSS, VSSA) pins must always be connected to the external power supply, in the permitted range.
- 2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.
- 3. A positive injection is induced by  $V_{IN} > V_{DDIOx}$  while a negative injection is induced by  $V_{IN} < V_{SS}$ .  $I_{INJ(PIN)}$  must never be exceeded. Refer to *Table 20: Voltage characteristics* for the maximum allowed input voltage values.
- 4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
- On these I/Os, a positive injection is induced by V<sub>IN</sub> > V<sub>DDA</sub>. Negative injection disturbs the analog performance of the device. See note <sup>(2)</sup> below *Table 57: ADC accuracy*.
- When several inputs are submitted to a current injection, the maximum ΣI<sub>INJ(PIN)</sub> is the absolute sum of the positive and negative injected currents (instantaneous values).

**Table 22. Thermal characteristics** 

Symbol	Ratings	Value	Unit
T <sub>STG</sub>	Storage temperature range	-65 to +150	°C
T <sub>J</sub>	Maximum junction temperature	150	°C

## 6.3 Operating conditions

## 6.3.1 General operating conditions

Table 23. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit	
f <sub>HCLK</sub>	Internal AHB clock frequency	-	0	48	MHz	
f <sub>PCLK</sub>	Internal APB clock frequency	-	0	48	IVIIIZ	
$V_{DD}$	Standard operating voltage	-	1.65	1.95	V	
V <sub>DDIO2</sub>	I/O supply voltage	Must not be supplied if V <sub>DD</sub> is not present	1.65	3.6	V	
V	Analog operating voltage (ADC and DAC not used)	Must have a potential equal	$V_{DD}$	3.6	\/	
$V_{DDA}$	Analog operating voltage (ADC and DAC used)	to or higher than V <sub>DD</sub>	2.4	3.6	V	
$V_{BAT}$	Backup operating voltage	-	1.65	3.6	V	
		TC and RST I/O	-0.3	V <sub>DDIOx</sub> +0.3		
$V_{IN}$	I/O input voltage	TTa and POR I/O	-0.3	V <sub>DDA</sub> +0.3 <sup>(1)</sup>	V	
		FT and FTf I/O	-0.3	5.2 <sup>(1)</sup>		
		UFBGA100	-	364		
		LQFP100	-	476		
	Power dissipation at T <sub>A</sub> = 85 °C	LQFP64	-	455		
$P_{D}$	for suffix 6 or T <sub>A</sub> = 105 °C for suffix 7 <sup>(2)</sup>	WLCSP64	-	377	mW	
	suffix 7 <sup>(2)</sup>	UFBGA64	-	308		
		LQFP48	-	370		
		UFQFPN48	-	625		
	Ambient temperature for the	Maximum power dissipation	-40	85	°C	
т.	suffix 6 version	Low power dissipation <sup>(3)</sup>	-40	105	C	
TA	Ambient temperature for the	Maximum power dissipation	-40	105	°C	
	suffix 7 version	Low power dissipation <sup>(3)</sup>	-40	125	°C	

<sup>1.</sup> For operation with a voltage higher than  $V_{DDIOx}$  + 0.3 V, the internal pull-up resistor must be disabled.

## 6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 24* are derived from tests performed under the ambient temperature condition summarized in *Table 23*.

<sup>2.</sup> If  $T_A$  is lower, higher  $P_D$  values are allowed as long as  $T_J$  does not exceed  $T_{Jmax}$ . See

In low power dissipation state, T<sub>A</sub> can be extended to this range as long as T<sub>J</sub> does not exceed T<sub>Jmax</sub> (see Section 7.8: Thermal characteristics)

Symbol	Parameter	Conditions	Min	Max	Unit
t	V <sub>DD</sub> rise time rate		0	8	
$t_{VDD}$	V <sub>DD</sub> fall time rate	-	20	∞	μs/V
	V <sub>DDA</sub> rise time rate		0	∞	μ5/ ν
t <sub>VDDA</sub>	V <sub>DDA</sub> fall time rate	-	20	∞	

Table 24. Operating conditions at power-up / power-down

### 6.3.3 Embedded reference voltage

The parameters given in *Table 25* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>REFINT</sub>	Internal reference voltage	-40 °C < T <sub>A</sub> < +105 °C	1.16	1.2	1.25	V
t <sub>START</sub>	ADC_IN17 buffer startup time	-	-	-	10 <sup>(1)</sup>	μs
t <sub>S_vrefint</sub>	ADC sampling time when reading the internal reference voltage	-	4 <sup>(1)</sup>	-	-	μs
$\Delta V_{REFINT}$	Internal reference voltage spread over the temperature range	V <sub>DDA</sub> = 3 V	ı	-	10 <sup>(1)</sup>	mV
T <sub>Coeff</sub>	Temperature coefficient	-	- 100 <sup>(1)</sup>	-	100 <sup>(1)</sup>	ppm/°C
T <sub>VREFINT_RDY</sub>	Internal reference voltage temporization	-	1.5	2.5	4.5	ms

Table 25. Embedded internal reference voltage

#### 6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 14: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.



<sup>1.</sup> Guaranteed by design, not tested in production.

Guaranteed by design, not tested in production. This parameter is the latency between the time when pin NPOR is set to 1 by the application and the time when the VREFINTRDYF status bit is set to 1 by the hardware.

### Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f<sub>HCLK</sub> frequency:
  - 0 wait state and Prefetch OFF from 0 to 24 MHz
  - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled f<sub>PCLK</sub> = f<sub>HCLK</sub>

The parameters given in *Table 26* to *Table 29* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.



Table 26. Typical and maximum current consumption from  $V_{DD}$  supply at  $V_{DD}$  = 1.8 V

		to. Typical al			II periphe				periphe			
Symbol	Parameter	Conditions	f <sub>HCLK</sub>		N	lax @ T <sub>A</sub>	(1)		М	ax @ T <sub>A</sub>	(1)	Unit
Sy	Para			Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C	
		HSI48	48 MHz	26.2	28.0	28.8	28.9	14.2	15.1	15.2	15.3	
	Supply current in Run mode, code executing from Flash memory		48 MHz	26.1	27.9	28.7	28.8	14.1	15.0	15.1	15.3	
		HSE bypass, PLL on	32 MHz	17.7	18.9	19.4	19.5	9.6	10.2	10.3	10.4	
	ın m ash r		24 MHz	13.8	14.6	14.9	15.0	7.9	8.2	8.4	8.6	
	n R	HSE bypass,	8 MHz	4.7	5.0	5.1	5.3	2.7	2.9	2.9	2.9	
	ent i	PLL off	1 MHz	8.0	0.9	1.0	1.1	0.6	0.7	8.0	8.0	
	curr		48 MHz	26.1	27.9	28.7	28.9	14.1	15.0	15.2	15.3	
	pply	HSI clock, PLL on	32 MHz	17.8	19.0	19.4	19.5	9.7	10.2	10.4	10.4	
	Sul de e		24 MHz	13.9	14.7	15.0	15.1	8.0	8.3	8.5	8.7	
	8	HSI clock, PLL off	8 MHz	4.8	5.1	5.1	5.4	2.7	2.9	2.9	2.9	m ^
		HSI48	48 MHz	25.7	27.6	28.2	28.5	13.6	14.6	14.7	14.9	mA
		HSE bypass, PLL on	48 MHz	25.5	27.4	28.1	28.3	13.5	14.5	14.7	14.8	
	ode, √M		32 MHz	17.2	18.4	18.9	19.0	9.1	9.7	9.9	9.9	
	E E		24 MHz	13.1	14.0	14.3	14.4	7.1	7.5	7.7	7.8	
	n Ru y froi	HSE bypass,	8 MHz	4.2	4.6	4.7	4.8	2.3	2.5	2.5	2.6	
I <sub>DD</sub>	ent ii uting	PLL off	1 MHz	0.5	0.7	0.7	0.7	0.3	0.4	0.4	0.5	
	Supply current in Run mode, code executing from RAM		48 MHz	25.6	27.5	28.2	28.4	13.6	14.5	14.7	14.8	
	oply	HSI clock, PLL on	32 MHz	17.3	18.5	18.9	19.0	9.1	9.8	9.9	10.0	
	Sul		24 MHz	13.2	14.1	14.4	14.4	7.2	7.6	7.8	7.9	
		HSI clock, PLL off	8 MHz	4.4	4.7	4.9	4.9	2.3	2.6	2.6	2.6	
		HSI48	48 MHz	16.5	17.7	18.2	18.3	3.1	3.4	3.5	3.6	
			48 MHz	16.4	17.6	18.0	18.1	3.1	3.3	3.4	3.5	
	pode	HSE bypass, PLL on	32 MHz	11.1	11.9	12.2	12.3	2.1	2.3	2.4	2.5	
	eb n		24 MHz	8.4	9.1	9.3	9.4	1.6	1.8	1.9	2.0	
	Sle	HSE bypass,	8 MHz	2.8	3.0	3.1	3.4	0.5	0.7	0.7	0.8	
	urrent in PTF off	PLL off	1 MHz	0.4	0.5	0.5	0.6	0.2	0.3	0.3	0.4	mA
		48 MHz	16.4	17.7	18.1	18.2	3.1	3.3	3.4	3.5		
	) dd	HSI clock, PLL on	32 MHz	11.2	12.0	12.2	12.3	2.2	2.4	2.5	2.6	
	Iddns PLL on	24 MHz	8.5	9.1	9.3	9.4	1.7	1.8	1.9	2.0		
		HSI clock, PLL off	8 MHz	2.8	3.1	3.1	3.5	0.6	0.7	0.7	0.8	



1. Data based on characterization results, not tested in production unless otherwise specified.

Table 27. Typical and maximum current consumption in Stop mode

		SI		Typ @ V <sub>DDA</sub> (V <sub>DD</sub> = 1.8 V)							Max		
Symbol	Parameter	Conditions	= 1.8 V	= 2.0 V	= 2.4 V	= 2.7 V	= 3.0 V	= 3.3 V	= 3.6 V	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit
I <sub>DD</sub>	Supply current	pply current				0.6				2.4	33	78	
I <sub>DDA</sub>	in Stop mode	All oscillators OFF	0.9	0.9	1.0	1.0	1.0	1.1	1.2	2.5	3.0	3.7	μA

Table 28. Typical and maximum current consumption from the  $V_{\text{DDA}}$  supply

	er				V <sub>DDA</sub>	= 2.4 V	•		V <sub>DDA</sub>	= 3.6 \	/	
Symbol	Para-meter	Conditions (1)	f <sub>HCLK</sub>		Max @ T <sub>A</sub> <sup>(2)</sup>				M	ax @ T,	A <sup>(2)</sup>	Unit
	Para			Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C	
		HSI48	48 MHz	311	332	337	346	315	333	340	349	
		HSE	48 MHz	146	167	177	180	159	180	191	196	
	Supply current in	bypass, PLL on  HSE bypass, PLL off	32 MHz	100	118	124	126	108	126	134	137	
	Run or		24 MHz	79	95	98	99	85	100	105	108	
	Sleep mode,		8 MHz	2	3	3	4	3	3	4	4	
I <sub>DDA</sub>	code executing		1 MHz	2	2	3	3	2	3	3	4	μΑ
	from		48 MHz	212	242	253	257	234	261	274	280	
Flash memory or RAM	HSI clock, PLL on	32 MHz	165	193	202	203	183	206	215	219		
	or RAM	,	24 MHz	143	170	176	177	160	179	186	189	
		HSI clock, PLL off	8 MHz	64	82	84	85	76	88	91	92	

Current consumption from the V<sub>DDA</sub> supply is independent of whether the digital peripherals are enabled or disabled, being in Run or Sleep mode or executing from Flash memory or RAM. Furthermore, when the PLL is off, I<sub>DDA</sub> is independent from the frequency.



<sup>2.</sup> Data based on characterization results, not tested in production unless otherwise specified.

	Parameter	Conditions			Тур @	V <sub>BAT</sub>						
Symbol			1.65 V	1.8 V	2.4 V	2.7 V	3.3 V	3.6 V	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit
I <sub>DD_VBAT</sub> supply	domain	LSE & RTC ON; "Xtal mode": lower driving capability; LSEDRV[1:0] = '00'	0.5	0.5	0.6	0.7	0.9	1.0	1.0	1.3	1.8	шА
	supply current	LSE & RTC ON; "Xtal mode" higher driving capability; LSEDRV[1:0] = '11'	0.8	0.8	0.9	1.0	1.2	1.3	1.4	1.7	2.2	μА

Table 29. Typical and maximum current consumption from the V<sub>BAT</sub> supply

#### **Typical current consumption**

The MCU is placed under the following conditions:

- V<sub>DD</sub> = V<sub>DDA</sub> = 1.8 V
- All I/O pins are in analog input configuration
- The Flash memory access time is adjusted to f<sub>HCLK</sub> frequency:
  - 0 wait state and Prefetch OFF from 0 to 24 MHz
  - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled, f<sub>PCLK</sub> = f<sub>HCLK</sub>
- PLL is used for frequencies greater than 8 MHz
- AHB prescaler of 2, 4, 8 and 16 is used for the frequencies 4 MHz, 2 MHz, 1 MHz and 500 kHz respectively



<sup>1.</sup> Data based on characterization results, not tested in production.

Table 30. Typical current consumption, code executing from Flash memory, running from HSE 8 MHz crystal

Symbol	Parameter	£	Typical con Run i	sumption in mode		sumption in mode	Unit
Symbol	Parameter	f <sub>HCLK</sub>	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Oilit
		48 MHz	26.1	14.3	16.8	3.4	
		36 MHz	20.2	11.1	13.0	2.8	
		32 MHz	18.5	10.3	11.7	2.5	
	Current	24 MHz	14.5	8.1	9.1	1.9	
I==	consumption	16 MHz	10.1	5.7	6.3	1.4	mA
I <sub>DD</sub>	from V <sub>DD</sub> supply	8 MHz	5.0	2.8	2.9	0.7	ША
	Supply	4 MHz	3.1	1.8	1.9	0.6	
		2 MHz	1.8	1.1	1.3	0.6	
		1 MHz	1.2	0.8	1.0	0.5	
		500 kHz	1.0	0.7	0.9	0.5	
		48 MHz		1	51		
		36 MHz		1	18		
		32 MHz		10	08		
	Current	24 MHz		8	7		
l	consumption	16 MHz		6	3		μΑ
I <sub>DDA</sub>	from V <sub>DDA</sub> supply	8 MHz		1	.1		μΛ
	Зирріу	4 MHz		1	.1		
		2 MHz		1	.1		
		1 MHz		1	.1		
		500 kHz		1	.1		

#### I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

#### I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 50: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt



trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution:

Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

#### I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 32: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

 $I_{\mbox{\scriptsize SW}}$  is the current sunk by a switching I/O to charge/discharge the capacitive load

V<sub>DDIOx</sub> is the I/O supply voltage

f<sub>SW</sub> is the I/O switching frequency

C is the total capacitance seen by the I/O pin:  $C = C_{INT} + C_{EXT} + C_{S}$ 

C<sub>S</sub> is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.



Table 31. Switching output I/O current consumption

Symbol	Parameter	Conditions <sup>(1)</sup>	I/O toggling frequency (f <sub>SW</sub> )	Тур	Unit		
			2 MHz	0.09			
			4 MHz	0.17			
		$V_{DDIOx} = 1.8 V$ $C_{EXT} = 0 pF$	8 MHz	0.34			
		$C = C_{INT} + C_{EXT} + C_{S}$	18 MHz	0.79			
		IIVI EXI O	36 MHz	1.50			
			48 MHz	2.06			
			2 MHz	0.13			
			4 MHz	0.26			
		V <sub>DDIOx</sub> = 1.8 V	8 MHz	0.50			
		$C_{EXT} = 10 \text{ pF}$ $C = C_{INT} + C_{EXT} + C_{S}$	18 MHz	1.18	mA		
	I/O current consumption		36 MHz	2.27			
			48 MHz	3.03			
		$V_{DDIOx} = 1.8 V$ $C_{EXT} = 22 pF$ $C = C_{INT} + C_{EXT} + C_{S}$	2 MHz	0.18			
I <sub>SW</sub>			4 MHz	0.36			
			8 MHz	0.69			
			18 MHz	1.60			
			36 MHz	3.27			
			2 MHz	0.23			
		V <sub>DDIOx</sub> = 1.8 V	4 MHz	0.45			
		C <sub>EXT</sub> = 33 pF	8 MHz	0.87			
		$C = C_{INT} + C_{EXT} + C_{S}$	18 MHz	2.0			
			36 MHz	3.7			
			2 MHz	0.29			
		$V_{DDIOx} = 1.8 \text{ V}$	4 MHz	0.55			
		$C_{EXT} = 47 \text{ pF}$ $C = C_{INT} + C_{EXT} + C_{S}$			8 MHz	1.09	
		2, 0	18 MHz	2.43			

<sup>1.</sup>  $C_S = 5 pF$  (estimated value).



#### On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 32*. The MCU is placed under the following conditions:

- All I/O pins are in analog mode
- All peripherals are disabled unless otherwise mentioned
- The given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- Ambient operating temperature and supply voltage conditions summarized in *Table 20: Voltage characteristics*

Table 32. Peripheral current consumption

Peripheral		Typical consumption at 25 °C	Unit
	BusMatrix <sup>(1)</sup>	3.1	
	CRC	2.0	
	DMA1	5.5	
	DMA2	5.1	
	Flash memory interface	15.4	
	GPIOA	5.5	
AHB	GPIOB	5.4	μΑ/MHz
AHD	GPIOC	3.2	μΑνίνιι ιΖ
	GPIOD	3.1	
	GPIOE	4.0	
	GPIOF	2.5	
	SRAM	0.8	
	TSC	5.5	
	All AHB peripherals	61.0	

Table 32. Peripheral current consumption (continued)

APB-Bridge (2)   3.6     ADC (3)		Table 32. Peripheral current consumption (continued)						
ADC <sup>(3)</sup> CAN 12.4 CEC 0.4 CRS 0.0 DAC <sup>(3)</sup> DBG (MCU Debug Support) 0.2 I2C1 2.9 I2C2 2.4 PWR 0.6 SPI1 8.8 SPI2 7.8 SYSCFG and COMP 1.9 TIM1 15.2 TIM14 2.6 TIM15 8.7 TIM16 5.8 TIM17 7.0 TIM2 16.2 TIM3 11.9 TIM6 11.8 TIM7 2.5 USART1 17.6 USART1 17.6 USART2 16.3 USART4 4.7 USART5 4.4 USART5 4.4 USART6 5.5 USART8 5.1 WWDG 1.1			Typical consumption at 25 °C	Unit				
CAN 12.4  CEC 0.4  CRS 0.0  DAC <sup>(3)</sup> 4.2  DBG (MCU Debug Support) 0.2  IZC1 2.9  IZC2 2.4  PWR 0.6  SPI1 8.8  SPI2 7.8  SYSCFG and COMP 1.9  TIM1 15.2  TIM14 2.6  TIM15 8.7  TIM16 5.8  TIM17 7.0  TIM2 16.2  TIM3 11.9  TIM6 11.8  TIM7 2.5  USART1 17.6  USART3 16.2  USART4 4.7  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1			3.6					
CEC 0.4 CRS 0.0 DAC <sup>(3)</sup> 4.2 DBG (MCU Debug Support) 0.2 I2C1 2.9 I2C2 2.4 PWR 0.6 SPI1 8.8 SPI2 7.8 SYSCFG and COMP 1.9 TIM1 15.2 TIM14 2.6 TIM15 8.7 TIM16 5.8 TIM17 7.0 TIM2 16.2 TIM3 11.9 TIM6 11.8 TIM7 2.5 USART1 17.6 USART1 17.6 USART2 16.3 USART3 16.2 USART4 4.7 USART5 4.4 USART6 5.5 USART7 5.2 USART8 5.1 WWDG 1.1		ADC <sup>(3)</sup>	4.3					
CRS 0.0 DAC <sup>(3)</sup> 4.2 DBG (MCU Debug Support) 0.2 I2C1 2.9 I2C2 2.4 PWR 0.6 SPI1 8.8 SPI2 7.8 SYSCFG and COMP 1.9 TIM1 15.2 TIM14 2.6 TIM15 8.7 TIM16 5.8 TIM17 7.0 TIM2 16.2 TIM2 16.2 TIM3 11.9 TIM6 11.8 TIM7 2.5 USART1 17.6 USART2 16.3 USART3 16.2 USART4 4.7 USART5 4.4 USART6 5.5 USART7 5.2 USART8 WWDG 1.1		CAN	12.4					
DAC <sup>(3)</sup> DBG (MCU Debug Support)  12C1 2.9 12C2 2.4 PWR 0.6 SPI1 8.8 SPI2 7.8 SYSCFG and COMP 1.9 TIM1 15.2 TIM14 2.6 TIM15 8.7 TIM16 5.8 TIM17 7.0 TIM2 16.2 TIM3 11.9 TIM6 11.8 TIM7 2.5 USART1 USART1 USART5 USART7 5.2 USART8 USART7 5.2 USART8 USART8 5.1 WWDG 1.1		CEC	0.4					
DBG (MCU Debug Support)  I2C1  I2C2  I2C2  PWR  0.6  SPI1  8.8  SPI2  7.8  SYSCFG and COMP  1.9  TIM1  15.2  TIM14  2.6  TIM15  8.7  TIM16  5.8  TIM17  7.0  TIM2  11.8  TIM3  11.9  TIM6  11.8  TIM7  2.5  USART1  USART5  USART5  USART7  USART7  USART7  USART8  SPI2  7.8  8.8  ABB  ABB  ABB  ABB  ABB  ABB  A			0.0					
I2C1		DAC <sup>(3)</sup>	4.2					
I2C2		DBG (MCU Debug Support)	0.2					
PWR		I2C1	2.9					
SPI1 8.8 SPI2 7.8 SYSCFG and COMP 1.9 TIM1 15.2 TIM14 2.6 TIM15 8.7 TIM16 5.8 TIM17 7.0 TIM2 16.2 TIM3 11.9 TIM6 11.8 TIM7 2.5 USART1 17.6 USART2 16.3 USART3 16.2 USART4 4.7 USART5 4.4 USART5 4.4 USART6 5.5 USART7 5.2 USART8 5.1 WWDG 1.1		I2C2	2.4					
SPI2 7.8 SYSCFG and COMP 1.9 TIM1 15.2 TIM14 2.6 TIM15 8.7 TIM16 5.8 TIM17 7.0 TIM2 16.2 TIM3 11.9 TIM6 11.8 TIM7 2.5 USART1 17.6 USART2 16.3 USART3 16.2 USART4 4.7 USART5 4.4 USART6 5.5 USART7 5.2 USART8 5.1 WWDG 1.1		PWR	0.6					
SYSCFG and COMP TIM1 15.2 TIM14 2.6 TIM15 8.7 TIM16 5.8 TIM17 7.0 TIM2 16.2 TIM3 11.9 TIM6 11.8 TIM7 2.5 USART1 USART2 USART4 USART5 USART6 USART7 5.2 USART8 WWDG 1.1		SPI1	8.8					
TIM1 15.2  TIM14 2.6  TIM15 8.7  TIM16 5.8  TIM17 7.0  TIM2 16.2  TIM3 11.9  TIM6 11.8  TIM7 2.5  USART1 17.6  USART2 16.3  USART3 16.2  USART4 4.7  USART5 4.4  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1		SPI2	7.8					
TIM14 2.6  TIM15 8.7  TIM16 5.8  TIM17 7.0  TIM2 16.2  TIM3 11.9  TIM6 11.8  TIM7 2.5  USART1 17.6  USART2 16.3  USART3 16.2  USART4 4.7  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1		SYSCFG and COMP	1.9					
TIM15 TIM16 TIM17 TIM2 TIM2 TIM3 TIM6 TIM7 TIM6 TIM7 TIM6 TIM7 2.5 USART1 USART2 USART3 USART4 USART5 USART6 USART7 TUSART8 TUSART8 TUSART8 TUSART8 TIM15  8.7  μΑ/ΜΗΖ μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μΑ/ΜΗΖ  μα/ΜΗΣ  μα/ΜΗΖ  μα/ΜΕΣ  μα/μα/μα/μα/μα/μα/μα/μα/μα/μα/μα/μα/μα/μ		TIM1	15.2					
TIM16  TIM17  TIM2  TIM3  TIM6  TIM7  2.5  USART1  USART2  USART3  USART4  USART5  USART5  USART6  USART7  USART7  USART7  USART8  USART8  USART8  TIM16  5.8  µA/MHz	TIM14	2.6						
TIM16 TIM17 TIM2 TIM2 TIM3 TIM6 TIM6 TIM7 TIM6 TIM7 2.5 USART1 17.6 USART2 USART3 16.2 USART4 USART5 USART5 USART6 USART7 TUSART7 TUSART7 TUSART7 TUSART7 TUSART7 TUSART7 TUSART7 TUSART8 TIM7 TIM6 TIM9 TIM9 TIM9 TIM9 TIM9 TIM9 TIM9 TIM9	ADD	TIM15	8.7	0 /0 /1 !				
TIM2 16.2  TIM3 11.9  TIM6 11.8  TIM7 2.5  USART1 17.6  USART2 16.3  USART3 16.2  USART4 4.7  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1	APB	TIM16	5.8	μΑνίνιπε				
TIM3 11.9  TIM6 11.8  TIM7 2.5  USART1 17.6  USART2 16.3  USART3 16.2  USART4 4.7  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1		TIM17	7.0					
TIM6 11.8  TIM7 2.5  USART1 17.6  USART2 16.3  USART3 16.2  USART4 4.7  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1		TIM2	16.2					
TIM7       2.5         USART1       17.6         USART2       16.3         USART3       16.2         USART4       4.7         USART5       4.4         USART6       5.5         USART7       5.2         USART8       5.1         WWDG       1.1		TIM3	11.9					
USART1 17.6  USART2 16.3  USART3 16.2  USART4 4.7  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1		TIM6	11.8					
USART2 16.3  USART3 16.2  USART4 4.7  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1		TIM7	2.5					
USART3 16.2  USART4 4.7  USART5 4.4  USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1		USART1	17.6					
USART4 4.7 USART5 4.4 USART6 5.5 USART7 5.2 USART8 5.1 WWDG 1.1		USART2	16.3					
USART5 4.4 USART6 5.5 USART7 5.2 USART8 5.1 WWDG 1.1		USART3	16.2					
USART6 5.5  USART7 5.2  USART8 5.1  WWDG 1.1		USART4	4.7					
USART7 5.2 USART8 5.1 WWDG 1.1		USART5	4.4					
USART8 5.1 WWDG 1.1		USART6	5.5					
WWDG 1.1		USART7	5.2					
		USART8	5.1					
All APB peripherals 207.2		WWDG	1.1					
		All APB peripherals	207.2					

- 1. The BusMatrix is automatically active when at least one master is ON (CPU, DMA).
- 2. The APB Bridge is automatically active when at least one peripheral is ON on the Bus.
- The power consumption of the analog part (I<sub>DDA</sub>) of peripherals such as ADC, DAC, comparators, is not included. Refer to the tables of characteristics in the subsequent sections.



#### 6.3.5 Wakeup time from low-power mode

The wakeup times given in *Table 33* are the latency between the event and the execution of the first user instruction. The device goes in low-power mode after the WFE (Wait For Event) instruction, in the case of a WFI (Wait For Interruption) instruction, 16 CPU cycles must be added to the following timings due to the interrupt latency in the Cortex M0 architecture.

The SYSCLK clock source setting is kept unchanged after wakeup from Sleep mode. During wakeup from Stop mode, SYSCLK takes the default setting: HSI 8 MHz.

The wakeup source from Sleep and Stop mode is an EXTI line configured in event mode.

All timings are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

	iable oo. Ion power meas harroup illin	90			
Symbol	Parameter		V <sub>DDA</sub>	Max	Unit
			= 3.3 V		Oilit
t <sub>WUSTOP</sub>	Wakeup from Stop mode	3.5	2.8	5.3	μs
t <sub>WUSLEEP</sub>	Wakeup from Sleep mode	4 SYSCI	K cycles	-	μs

Table 33. Low-power mode wakeup timings

#### 6.3.6 External clock source characteristics

#### High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in *Section 6.3.13*. However, the recommended clock input waveform is shown in *Figure 15: High-speed external clock source AC timing diagram*.

Symbol	Parameter <sup>(1)</sup>	Min	Тур	Max	Unit
f <sub>HSE_ext</sub>	User external clock source frequency	-	8	32	MHz
$V_{HSEH}$	OSC_IN input pin high level voltage	0.7 V <sub>DDIOx</sub>	-	$V_{DDIOx}$	V
V <sub>HSEL</sub>	OSC_IN input pin low level voltage	$V_{SS}$	-	0.3 V <sub>DDIOx</sub>	V
t <sub>w(HSEH)</sub>	OSC_IN high or low time	15	-	-	ns
$\begin{matrix} t_{r(\text{HSE})} \\ t_{f(\text{HSE})} \end{matrix}$	OSC_IN rise or fall time	-	-	20	113

Table 34. High-speed external user clock characteristics



<sup>1.</sup> Guaranteed by design, not tested in production.

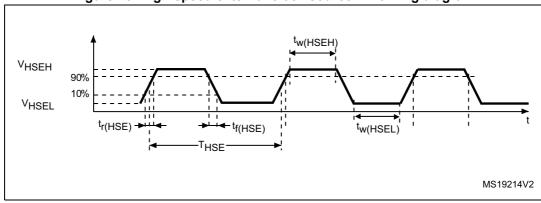


Figure 15. High-speed external clock source AC timing diagram

#### Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in Section 6.3.13. However, the recommended clock input waveform is shown in Figure 16.

Symbol	Parameter <sup>(1)</sup>	Min	Тур	Max	Unit
f <sub>LSE_ext</sub>	User external clock source frequency	-	32.768	1000	kHz
V <sub>LSEH</sub>	OSC32_IN input pin high level voltage	0.7 V <sub>DDIOx</sub>	-	$V_{DDIOx}$	V
V <sub>LSEL</sub>	OSC32_IN input pin low level voltage	V <sub>SS</sub>	-	0.3 V <sub>DDIOx</sub>	٧
$\begin{matrix} t_{w(\text{LSEH})} \\ t_{w(\text{LSEL})} \end{matrix}$	OSC32_IN high or low time	450	-	-	ns
t <sub>r(LSE)</sub>	, JOOGGE IN TISC OF IGHT WITH		-	50	113

Table 35. Low-speed external user clock characteristics

<sup>1.</sup> Guaranteed by design, not tested in production.

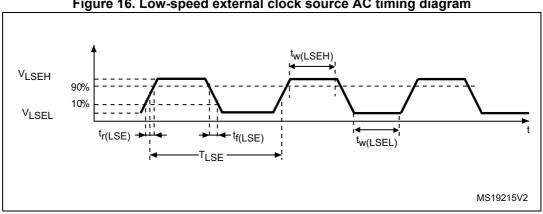


Figure 16. Low-speed external clock source AC timing diagram

#### High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 36*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions <sup>(1)</sup>	Min <sup>(2)</sup>	Тур	Max <sup>(2)</sup>	Unit
f <sub>OSC_IN</sub>	Oscillator frequency	-	4	8	32	MHz
R <sub>F</sub>	Feedback resistor	-	-	200	-	kΩ
		During startup <sup>(3)</sup>	-		8.5	
		$V_{DD}$ = 1.8 V, Rm = 30 $\Omega$ CL = 10 pF@8 MHz	-	0.4	-	
		$V_{DD}$ = 1.8 V, Rm = 45 $\Omega$ CL = 10 pF@8 MHz	-	0.5	-	
I <sub>DD</sub>	HSE current consumption	V <sub>DD</sub> = 1.8 V, Rm = 30 Ω CL = 5 pF@32 MHz	-	0.8	-	mA
		V <sub>DD</sub> = 1.8 V, Rm = 30 Ω CL = 10 pF@32 MHz	-	1	-	
		V <sub>DD</sub> = 1.8 V, Rm = 30 Ω CL = 20 pF@32 MHz	-	1.5	-	
9 <sub>m</sub>	Oscillator transconductance	Startup	10	-	-	mA/V
t <sub>SU(HSE)</sub> <sup>(4)</sup>	Startup time	V <sub>DD</sub> is stabilized	-	2	-	ms

Table 36. HSE oscillator characteristics

- 1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
- 2. Guaranteed by design, not tested in production.
- 3. This consumption level occurs during the first 2/3 of the  $t_{\mbox{\scriptsize SU(HSE)}}$  startup time
- 4. t<sub>SU(HSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For  $C_{L1}$  and  $C_{L2}$ , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*).  $C_{L1}$  and  $C_{L2}$  are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of  $C_{L1}$  and  $C_{L2}$ . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing  $C_{L1}$  and  $C_{L2}$ .

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



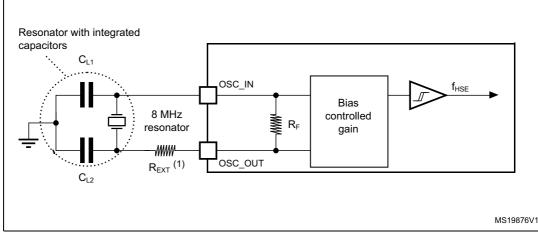


Figure 17. Typical application with an 8 MHz crystal

1.  $R_{\text{EXT}}$  value depends on the crystal characteristics.

#### Low-speed external clock generated from a crystal resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 37*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Conditions<sup>(1)</sup> **Symbol** Min<sup>(2)</sup> Тур Max<sup>(2)</sup> Unit **Parameter** LSEDRV[1:0]=00 0.5 0.9 lower driving capability LSEDRV[1:0]= 01 medium low driving capability LSE current consumption μΑ  $I_{DD}$ LSEDRV[1:0] = 10 1.3 medium high driving capability LSEDRV[1:0]=11 1.6 higher driving capability

Table 37. LSE oscillator characteristics (f<sub>LSE</sub> = 32.768 kHz)

Symbol	Parameter	Conditions <sup>(1)</sup>	Min <sup>(2)</sup>	Тур	Max <sup>(2)</sup>	Unit	
Oscillator g <sub>m</sub> transconductance		LSEDRV[1:0]=00 lower driving capability		5	-	-	
	LSEDRV[1:0]= 01 medium low driving capability		ı	-	µA/V		
	transconductance	LSEDRV[1:0] = 10 medium high driving capability	15	-	-	μΑνν	
		LSEDRV[1:0]=11 higher driving capability	25		-		
t <sub>SU(LSE)</sub> <sup>(3)</sup>	Startup time	V <sub>DDIOx</sub> is stabilized	-	2	-	s	

Table 37. LSE oscillator characteristics ( $f_{LSE} = 32.768 \text{ kHz}$ )

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Resonator with integrated capacitors

OSC32\_IN

Drive programmable amplifier

OSC32\_OUT

OSC32\_OUT

MS30253V2

Figure 18. Typical application with a 32.768 kHz crystal

Note:

70/127

An external resistor is not required between OSC32\_IN and OSC32\_OUT and it is forbidden to add one.

#### 6.3.7 Internal clock source characteristics

The parameters given in *Table 38* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*. The provided curves are characterization results, not tested in production.

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Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".

<sup>2.</sup> Guaranteed by design, not tested in production.

t<sub>SU(LSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

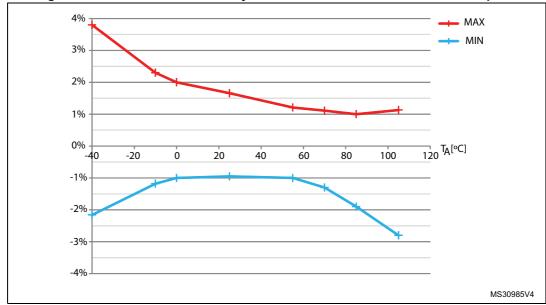
### High-speed internal (HSI) RC oscillator

Table 38. HSI oscillator characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSI</sub>	Frequency	-	-	8	-	MHz
TRIM	HSI user trimming step	-	-	-	1 <sup>(2)</sup>	%
DuCy <sub>(HSI)</sub>	Duty cycle	-	45 <sup>(2)</sup>	-	55 <sup>(2)</sup>	%
		$T_A = -40 \text{ to } 105^{\circ}\text{C}$	-2.8 <sup>(3)</sup>	-	3.8 <sup>(3)</sup>	
	Accuracy of the HSI oscillator	T <sub>A</sub> = -10 to 85°C	-1.9 <sup>(3)</sup>	-	2.3 <sup>(3)</sup>	%
ACC		T <sub>A</sub> = 0 to 85°C	-1.9 <sup>(3)</sup>	-	2 <sup>(3)</sup>	
ACC <sub>HSI</sub>		T <sub>A</sub> = 0 to 70°C	-1.3 <sup>(3)</sup>	-	2 <sup>(3)</sup>	70
		T <sub>A</sub> = 0 to 55°C	-1 <sup>(3)</sup>	-	2 <sup>(3)</sup>	
		$T_A = 25^{\circ}C^{(4)}$	-1	-	1	
t <sub>su(HSI)</sub>	HSI oscillator startup time	-	1 <sup>(2)</sup>	-	2 <sup>(2)</sup>	μs
I <sub>DDA(HSI)</sub>	HSI oscillator power consumption	-	-	80	100 <sup>(2)</sup>	μΑ

- 1.  $V_{DDA} = 3.3 \text{ V}$ ,  $T_A = -40 \text{ to } 105^{\circ}\text{C}$  unless otherwise specified.
- 2. Guaranteed by design, not tested in production.
- 3. Data based on characterization results, not tested in production.
- 4. Factory calibrated, parts not soldered.

Figure 19. HSI oscillator accuracy characterization results for soldered parts



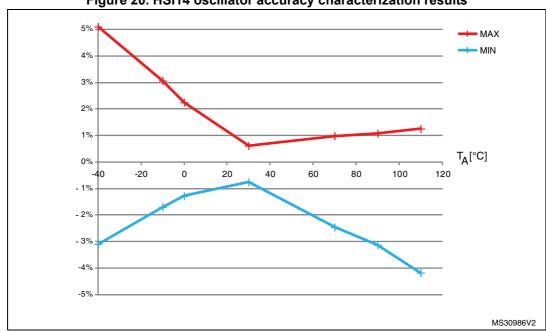
## High-speed internal 14 MHz (HSI14) RC oscillator (dedicated to ADC)

Table 39. HSI14 oscillator characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSI14</sub>	Frequency	-	-	14	-	MHz
TRIM	HSI14 user-trimming step	-	-	-	1 <sup>(2)</sup>	%
DuCy <sub>(HSI14)</sub>	Duty cycle	-	45 <sup>(2)</sup>	-	55 <sup>(2)</sup>	%
	Accuracy of the HSI14 oscillator (factory calibrated)	$T_A = -40 \text{ to } 105 ^{\circ}\text{C}$	-4.2 <sup>(3)</sup>	-	5.1 <sup>(3)</sup>	%
ACC		T <sub>A</sub> = -10 to 85 °C	$-3.2^{(3)}$	-	3.1 <sup>(3)</sup>	%
ACC <sub>HSI14</sub>		T <sub>A</sub> = 0 to 70 °C	-2.5 <sup>(3)</sup>	-	2.3 <sup>(3)</sup>	%
		T <sub>A</sub> = 25 °C	-1	-	1	%
t <sub>su(HSI14)</sub>	HSI14 oscillator startup time	-	1 <sup>(2)</sup>	-	2 <sup>(2)</sup>	μs
I <sub>DDA(HSI14)</sub>	HSI14 oscillator power consumption	-	-	100	150 <sup>(2)</sup>	μΑ

- 1.  $V_{DDA}$  = 3.3 V,  $T_{A}$  = -40 to 105 °C unless otherwise specified.
- 2. Guaranteed by design, not tested in production.
- 3. Data based on characterization results, not tested in production.

Figure 20. HSI14 oscillator accuracy characterization results



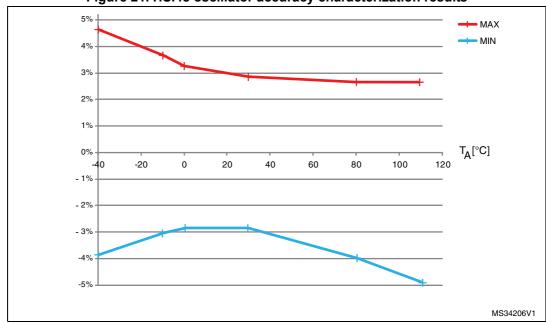
## High-speed internal 48 MHz (HSI48) RC oscillator

Table 40. HSI48 oscillator characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSI48</sub>	Frequency	-	-	48	-	MHz
TRIM	HSI48 user-trimming step	-	0.09 <sup>(2)</sup>	0.14	0.2 <sup>(2)</sup>	%
DuCy <sub>(HSI48)</sub>	Duty cycle	-	45 <sup>(2)</sup>	-	55 <sup>(2)</sup>	%
	Accuracy of the HSI48 oscillator (factory calibrated)	$T_A = -40 \text{ to } 105 ^{\circ}\text{C}$	-4.9 <sup>(3)</sup>	-	4.7 <sup>(3)</sup>	%
ACC		$T_A = -10 \text{ to } 85 ^{\circ}\text{C}$	-4.1 <sup>(3)</sup>	-	3.7 <sup>(3)</sup>	%
ACC <sub>HSI48</sub>		T <sub>A</sub> = 0 to 70 °C	-3.8 <sup>(3)</sup>	-	3.4 <sup>(3)</sup>	%
		T <sub>A</sub> = 25 °C	-2.8	-	2.9	%
t <sub>su(HSI48)</sub>	HSI48 oscillator startup time	-	-	-	6 <sup>(2)</sup>	μs
I <sub>DDA(HSI48)</sub>	HSI48 oscillator power consumption	-	-	312	350 <sup>(2)</sup>	μА

- 1.  $V_{DDA}$  = 3.3 V,  $T_{A}$  = -40 to 105 °C unless otherwise specified.
- 2. Guaranteed by design, not tested in production.
- 3. Data based on characterization results, not tested in production.

Figure 21. HSI48 oscillator accuracy characterization results



## Low-speed internal (LSI) RC oscillator

Table 41. LSI oscillator characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Тур	Max	Unit
f <sub>LSI</sub>	Frequency	30	40	50	kHz
t <sub>su(LSI)</sub> <sup>(2)</sup>		-	-	85	μs
I <sub>DDA(LSI)</sub> <sup>(2)</sup>	LSI oscillator power consumption	-	0.75	1.2	μΑ

<sup>1.</sup>  $V_{DDA}$  = 3.3 V,  $T_{A}$  = -40 to 105 °C unless otherwise specified.

## 6.3.8 PLL characteristics

The parameters given in *Table 42* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

Table 42. PLL characteristics

Symbol	Parameter		Unit		
Symbol	Farameter	Min	Тур	Max	Offic
f	PLL input clock <sup>(1)</sup>	1 <sup>(2)</sup>	8.0	24 <sup>(2)</sup>	MHz
f <sub>PLL_IN</sub>	PLL input clock duty cycle	40 <sup>(2)</sup>	-	60 <sup>(2)</sup>	%
f <sub>PLL_OUT</sub>	PLL multiplier output clock	16 <sup>(2)</sup>	-	48	MHz
t <sub>LOCK</sub>	PLL lock time	-	-	200 <sup>(2)</sup>	μs
Jitter <sub>PLL</sub>	Cycle-to-cycle jitter	-	-	300 <sup>(2)</sup>	ps

Take care to use the appropriate multiplier factors to obtain PLL input clock values compatible with the range defined by f<sub>PLL OUT</sub>.

## 6.3.9 Memory characteristics

## Flash memory

The characteristics are given at  $T_A$  = -40 to 105 °C unless otherwise specified.

Table 43. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Тур	Max <sup>(1)</sup>	Unit
t <sub>prog</sub>	16-bit programming time	$T_A = -40 \text{ to } +105 ^{\circ}\text{C}$	40	53.5	60	μs
t <sub>ERASE</sub>	Page (2 KB) erase time	T <sub>A</sub> = -40 to +105 °C	20	-	40	ms
t <sub>ME</sub>	Mass erase time	$T_A = -40 \text{ to } +105 ^{\circ}\text{C}$	20	-	40	ms
	Supply ourrant	Write mode	-	-	10	mA
I <sub>DD</sub>	Supply current	Erase mode	-	-	12	mA

<sup>1.</sup> Guaranteed by design, not tested in production.



<sup>2.</sup> Guaranteed by design, not tested in production.

<sup>2.</sup> Guaranteed by design, not tested in production.

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Unit
N <sub>END</sub>	Endurance	$T_A = -40 \text{ to } +105 ^{\circ}\text{C}$	10	kcycle
	Data retention	1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 85 °C	30	
t <sub>RET</sub>		1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 105 °C	10	Year
		10 kcycle <sup>(2)</sup> at T <sub>A</sub> = 55 °C	20	

Table 44. Flash memory endurance and data retention

- 1. Data based on characterization results, not tested in production.
- 2. Cycling performed over the whole temperature range.

### 6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

#### Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V<sub>DD</sub> and V<sub>SS</sub> through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 45*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	Parameter	Conditions	Level/ Class
V <sub>FESD</sub>	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD}$ = 1.8 V, LQFP100, $T_A$ = +25 °C, $f_{HCLK}$ = 48 MHz, conforming to IEC 61000-4-2	2B
V <sub>EFTB</sub>	Fast transient voltage burst limits to be applied through 100 pF on V <sub>DD</sub> and V <sub>SS</sub> pins to induce a functional disturbance	$V_{DD}$ = 1.8 V, LQFP100, $T_A$ = +25°C, $f_{HCLK}$ = 48 MHz, conforming to IEC 61000-4-4	4B

Table 45. EMS characteristics

## Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.



#### Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

#### Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

#### **Electromagnetic Interference (EMI)**

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Max vs. [f<sub>HSE</sub>/f<sub>HCLK</sub>] Monitored **Conditions** Unit Symbol **Parameter** frequency band 8/48 MHz 0.1 to 30 MHz 3  $V_{DD} = 1.8 \text{ V}, T_A = 25 \text{ °C}$ 30 to 130 MHz 23 dBuV LQFP100 package Peak level  $S_{EMI}$ compliant with 130 MHz to 1 GHz 15 IEC 61967-2 **EMI Level** 4

Table 46. EMI characteristics

## 6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

#### Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.



Symbol	Ratings	Conditions	Packages	Class	Maximum value <sup>(1)</sup>	Unit
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	T <sub>A</sub> = +25 °C, conforming to JESD22-A114	All	2	2000	V
V <sub>ESD(CDM)</sub>	Electrostatic discharge voltage (charge device model)	T <sub>A</sub> = +25 °C, conforming to ANSI/ESD STM5.3.1	WLCSP64, LQFP100	C3	250	V
,	(charge device moder)	TO ANSI/ESD STWIS.S. I	All others	C4	500	

Table 47. ESD absolute maximum ratings

### Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 48. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T <sub>A</sub> = +105 °C conforming to JESD78A	II level A

## 6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below  $V_{SS}$  or above  $V_{DDIOx}$  (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

### Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the -5  $\mu$ A/+0  $\mu$ A range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in *Table 49*.

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.



<sup>1.</sup> Data based on characterization results, not tested in production.

**Functional** susceptibility **Symbol** Description Unit **Positive** Negative injection injection Injected current on BOOT0 -0 NA Injected current on PF1 pin (FTf pin) -0 NA Injected current on PC0 pin (TTA pin) -0 +5 mΑ  $I_{IN,I}$ Injected current on PA4, PA5 pins with induced leakage NA -5 current on adjacent pins less than -20 µA Injected current on other FT and FTf pins, and on NPOR pin -5 NA Injected current on all other TC, TTa and RST pins -5 +5

Table 49. I/O current injection susceptibility

## 6.3.13 I/O port characteristics

#### General input/output characteristics

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the conditions summarized in *Table 23: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant.

Symbol **Parameter Conditions** Min Unit Тур Max TC and TTa I/O  $0.3 V_{DDIOx} + 0.07^{(1)}$ Low level input FT and FTf I/O 0.475 V<sub>DDIOx</sub>-0.2<sup>(1)</sup> V  $V_{IL}$ voltage All I/Os 0.3 V<sub>DDIOx</sub> TC and TTa I/O 0.445 V<sub>DDIOx</sub>+0.398<sup>(1)</sup> High level input  $0.5 V_{DDIOx} + 0.2^{(1)}$ FT and FTf I/O V  $V_{\text{IH}} \\$ voltage All I/Os 0.7 V<sub>DDIOx</sub> 200(1) TC and TTa I/O Schmitt trigger  $\mathrm{V}_{\mathrm{hys}}$ mV hysteresis  $100^{(1)}$ FT and FTf I/O TC. FT and FTf I/O TTa in digital mode  $\pm 0.1$  $V_{SS} \leq V_{IN} \leq V_{DDIOx}$ TTa in digital mode 1 Input leakage  $V_{DDIOx} \le V_{IN} \le V_{DDA}$ μΑ  $I_{lkq}$ current<sup>(2)</sup> TTa in analog mode  $\pm 0.2$  $V_{SS} \leq V_{IN} \leq V_{DDA}$ FT and FTf I/O 10  $V_{DDIOx} \le V_{IN} \le 5 V$ 

Table 50. I/O static characteristics



Table 50.	I/O static	characteristics	(continued)
I UDIO OU.	" O Statio	on an actor is the	(COIILIIGCA)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>PU</sub>	Weak pull-up equivalent resistor (3)	V <sub>IN</sub> = V <sub>SS</sub>	25	40	55	kΩ
R <sub>PD</sub>	Weak pull-down equivalent resistor <sup>(3)</sup>	$V_{IN} = V_{DDIOx}$	25	40	55	kΩ
C <sub>IO</sub>	I/O pin capacitance	-	-	5	-	pF

- 1. Data based on design simulation only. Not tested in production.
- The leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to Table 49: I/O current injection susceptibility.
- 3. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 22* for standard I/Os, and in *Figure 23* for 5 V-tolerant I/Os. The following curves are design simulation results, not tested in production.



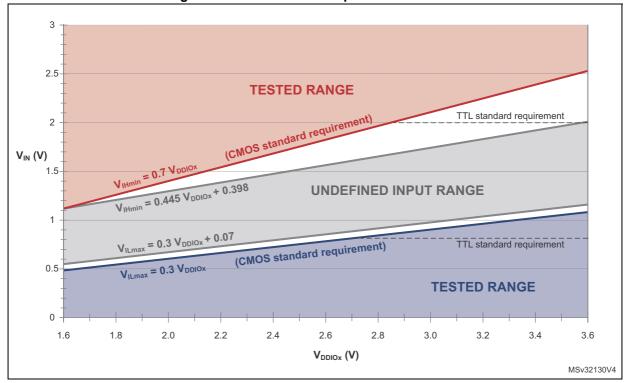
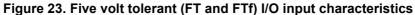
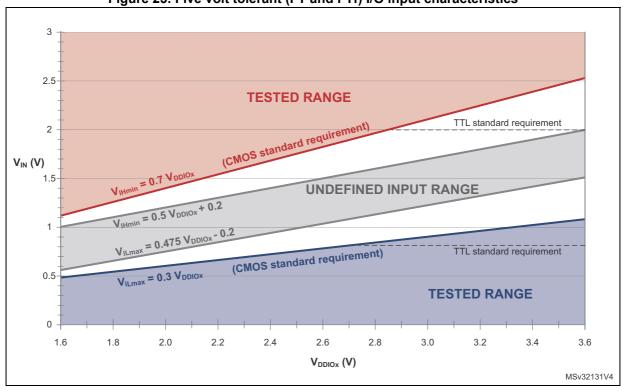


Figure 22. TC and TTa I/O input characteristics





## **Output driving current**

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed  $V_{OL}/V_{OH}$ ).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in Section 6.2:

- The sum of the currents sourced by all the I/Os on V<sub>DDIOX</sub>, plus the maximum consumption of the MCU sourced on V<sub>DD</sub>, cannot exceed the absolute maximum rating ΣI<sub>VDD</sub> (see *Table 20: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V<sub>SS</sub>, plus the maximum consumption of the MCU sunk on V<sub>SS</sub>, cannot exceed the absolute maximum rating ΣI<sub>VSS</sub> (see Table 20: Voltage characteristics).

## **Output voltage levels**

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT, TTa or TC unless otherwise specified).

Table 51. Output voltage characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>OL</sub>	Output low level voltage for an I/O pin	CMOS port <sup>(2)</sup>	-	0.4	.,
V <sub>OH</sub>	Output high level voltage for an I/O pin	$ I_{IO}  = 8 \text{ mA}$ $V_{DDIOx} \ge 2.7 \text{ V}$	V <sub>DDIOx</sub> -0.4	-	V
V <sub>OL</sub>	Output low level voltage for an I/O pin	TTL port <sup>(2)</sup>	-	0.4	.,
V <sub>OH</sub>	Output high level voltage for an I/O pin	$ I_{IO}  = 8 \text{ mA}$ $V_{DDIOx} \ge 2.7 \text{ V}$	2.4	-	V
V <sub>OL</sub> <sup>(3)</sup>	Output low level voltage for an I/O pin	I <sub>IO</sub>   = 20 mA	-	1.3	V
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage for an I/O pin	$V_{DDIOx} \ge 2.7 \text{ V}$	V <sub>DDIOx</sub> -1.3	-	
V <sub>OL</sub> <sup>(3)</sup>	Output low level voltage for an I/O pin	I <sub>IO</sub>   = 6 mA	-	0.4	V
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage for an I/O pin	V <sub>DDIOx</sub> ≥ 2 V	V <sub>DDIOx</sub> -0.4	-	V
V <sub>OL</sub> <sup>(4)</sup>	Output low level voltage for an I/O pin	II I = 4 m A	-	0.4	V
V <sub>OH</sub> <sup>(4)</sup>	Output high level voltage for an I/O pin	I <sub>IO</sub>   = 4 mA	V <sub>DDIOx</sub> -0.4	-	V
V <sub>OLFm+</sub> (3)	Output low level voltage for an FTf I/O pin in Fm+ mode	$ I_{IO}  = 20 \text{ mA}$ $V_{DDIOx} \ge 2.7 \text{ V}$	-	0.4	٧
	Triii+ mode	I <sub>IO</sub>   = 10 mA	-	0.4	V

The I<sub>IO</sub> current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 20:* Voltage characteristics, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI<sub>IO</sub>.

- 2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
- 3. Data based on characterization results. Not tested in production.
- 4. Data based on characterization results. Not tested in production.



## Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 24* and *Table 52*, respectively. Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

Table 52. I/O AC characteristics<sup>(1)(2)</sup>

OSPEEDRy [1:0] value <sup>(1)</sup>	Symbol	Parameter	Conditions	Min	Max	Unit	
	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>		-	2	MHz	
	t <sub>f(IO)out</sub>	Output fall time	$C_L = 50 \text{ pF}, V_{DDIOx} \ge 2 \text{ V}$	-	125		
x0	t <sub>r(IO)out</sub>	Output rise time		-	125	ns	
XU	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>		-	1	MHz	
	t <sub>f(IO)out</sub>	Output fall time	$C_L = 50 \text{ pF}, V_{DDIOx} < 2 \text{ V}$	-	125	ns	
	t <sub>r(IO)out</sub>	Output rise time		-	125	115	
	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>		-	10	MHz	
	t <sub>f(IO)out</sub>	Output fall time	$C_L = 50 \text{ pF}, V_{DDIOx} \ge 2 \text{ V}$	-	25	no	
01	t <sub>r(IO)out</sub>	Output rise time	1		25	ns	
01	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>			4	MHz	
	t <sub>f(IO)out</sub>	Output fall time	$C_L$ = 50 pF, $V_{DDIOx}$ < 2 V	-	62.5	ns	
	t <sub>r(IO)out</sub>	Output rise time		-	62.5	115	
			$C_L = 30 \text{ pF}, V_{DDIOx} \ge 2.7 \text{ V}$ $C_L = 50 \text{ pF}, V_{DDIOx} \ge 2.7 \text{ V}$	-	50		
	f 400 4	Maximum frequency <sup>(3)</sup>		ı	30	MHz	
	f <sub>max(IO)out</sub>	waximum requericy	$C_L$ = 50 pF, 2 V $\leq$ V <sub>DDIOx</sub> $<$ 2.7 V	-	20	IVIIIZ	
			$C_L$ = 50 pF, $V_{DDIOx}$ < 2 V	ı	10		
			$C_L = 30 \text{ pF}, V_{DDIOx} \ge 2.7 \text{ V}$	ı	5		
11	t	Output fall time	$C_L$ = 50 pF, $V_{DDIOx} \ge 2.7 \text{ V}$	ı	8		
	t <sub>f(IO)</sub> out	Output fail time	$C_L$ = 50 pF, 2 V $\leq$ V <sub>DDIOx</sub> $<$ 2.7 V	ı	12		
			C <sub>L</sub> = 50 pF, V <sub>DDIOx</sub> < 2 V		25	ns	
			$C_L = 30 \text{ pF}, V_{DDIOx} \ge 2.7 \text{ V}$	-	5	113	
	t and	Output rise time	$C_L = 50 \text{ pF}, V_{DDIOx} \ge 2.7 \text{ V}$	-	8	7	
	t <sub>r(IO)</sub> out	Output fise time	$C_L = 50 \text{ pF}, 2 \text{ V} \le V_{DDIOx} < 2.7 \text{ V}$	-	12		
			C <sub>L</sub> = 50 pF, V <sub>DDIOx</sub> < 2 V	-	25		



OSPEEDRy [1:0] value <sup>(1)</sup>	Symbol	Parameter	Conditions	Min	Max	Unit
	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>		-	2	MHz
	t <sub>f(IO)out</sub>	Output fall time	$C_L = 50 \text{ pF}, V_{DDIOx} \ge 2 \text{ V}$	-	12	
Fm+ configuration	t <sub>r(IO)out</sub>	Output rise time			34	ns
(4)	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>		ı	0.5	MHz
	t <sub>f(IO)out</sub>	Output fall time	C <sub>L</sub> = 50 pF, V <sub>DDIOx</sub> < 2 V	-	16	ns
	t <sub>r(IO)out</sub>	Output rise time		-	44	110
-	t <sub>EXTIpw</sub>	Pulse width of external signals detected by the EXTI controller	-	10	-	ns

Table 52. I/O AC characteristics<sup>(1)(2)</sup> (continued)

- The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32F0xxxx RM0091 reference manual for a description of GPIO Port configuration register.
- 2. Guaranteed by design, not tested in production.
- 3. The maximum frequency is defined in Figure 24.
- 4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the STM32F0xxxx reference manual RM0091 for a detailed description of Fm+ I/O configuration.

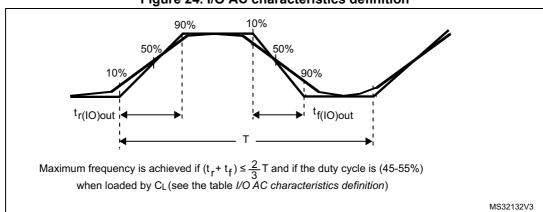


Figure 24. I/O AC characteristics definition

## 6.3.14 NRST and NPOR pin characteristics

## **NRST** pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor,  $R_{\text{PU}}$ .

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL(NRST)</sub>	NRST input low level voltage	-	-	ı	0.3 V <sub>DD</sub> +0.07 <sup>(1)</sup>	V
V <sub>IH(NRST)</sub>	NRST input high level voltage	-	0.445 V <sub>DD</sub> +0.398 <sup>(1)</sup>	ı	-	V
V <sub>hys(NRST)</sub>	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(2)</sup>	$V_{IN} = V_{SS}$	25	40	55	kΩ
V <sub>F(NRST)</sub>	NRST input filtered pulse	-	-	-	100 <sup>(1)</sup>	ns
V <sub>NF(NRST)</sub>	NRST input not filtered pulse	-	700 <sup>(1)</sup>	ı	-	ns

Table 53. NRST pin characteristics

The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (~10% order).

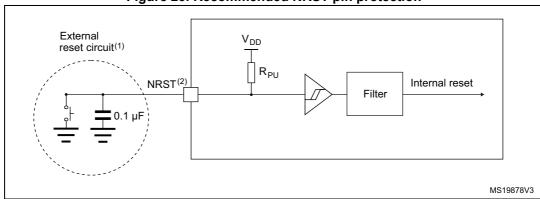


Figure 25. Recommended NRST pin protection

- 1. The external capacitor protects the device against parasitic resets.
- The user must ensure that the level on the NRST pin can go below the V<sub>IL(NRST)</sub> max level specified in Table 53: NRST pin characteristics. Otherwise the reset will not be taken into account by the device.

#### **NPOR** pin characteristics

The NPOR pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor to the  $V_{DDA}$ ,  $R_{PU}$ .

Unless otherwise specified, the parameters given in *Table 54* below are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

<sup>1.</sup> Data based on design simulation only. Not tested in production.

**Conditions** Unit **Symbol Parameter** Min Тур Max 0.475 V<sub>DDA</sub> - 0.2<sup>(1)</sup> NPOR Input low level voltage V<sub>IL(NPOR)</sub> ٧ NPOR Input high level  $0.5 V_{DDA} + 0.2^{(1)}$  $V_{IH(NPOR)}$ voltage NPOR Schmitt trigger voltage  $100^{(1)}$ mV V<sub>hys(NPOR)</sub> hysteresis Weak pull-up equivalent  $V_{IN} = V_{SS}$ 25 40 55  $\mathsf{k}\Omega$  $R_{PU}$ resistor<sup>(2)</sup>

Table 54. NPOR pin characteristics

### 6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 55* are derived from tests performed under the conditions summarized in *Table 23: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

**Table 55. ADC characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DDA</sub>	Analog supply voltage for ADC ON	-	2.4	-	3.6	V
I <sub>DDA (ADC)</sub>	Current consumption of the ADC <sup>(1)</sup>	V <sub>DDA</sub> = 3.3 V	-	0.9	-	mA
f <sub>ADC</sub>	ADC clock frequency	-	0.6	-	14	MHz
f <sub>S</sub> <sup>(2)</sup>	Sampling rate	12-bit resolution	0.043	-	1	MHz
f <sub>TRIG</sub> <sup>(2)</sup>	External trigger frequency	f <sub>ADC</sub> = 14 MHz, 12-bit resolution	-	-	823	kHz
		12-bit resolution	-	-	17	1/f <sub>ADC</sub>
V <sub>AIN</sub>	Conversion voltage range	-	0	-	$V_{DDA}$	٧
R <sub>AIN</sub> <sup>(2)</sup>	External input impedance	See Equation 1 and Table 56 for details	-	-	50	kΩ
R <sub>ADC</sub> <sup>(2)</sup>	Sampling switch resistance	-	-	-	1	kΩ
C <sub>ADC</sub> <sup>(2)</sup>	Internal sample and hold capacitor	-	-	-	8	pF
t <sub>CAL</sub> (2)(3)	Calibration time	f <sub>ADC</sub> = 14 MHz		5.9		μs
CAL (1)	Cambration time	- 83				1/f <sub>ADC</sub>

<sup>1.</sup> Guaranteed by design, not tested in production.

The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (~10% order).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	400.00	ADC clock = HSI14	1.5 ADC cycles + 2 f <sub>PCLK</sub> cycles	-	1.5 ADC cycles + 3 f <sub>PCLK</sub> cycles	
W <sub>LATENCY</sub> <sup>(2)(4)</sup>	ADC_DR register ready latency	ADC clock = PCLK/2	-	4.5	-	f <sub>PCLK</sub> cycle
		ADC clock = PCLK/4	-	8.5	-	f <sub>PCLK</sub> cycle
		$f_{ADC} = f_{PCLK}/2 = 14 \text{ MHz}$		0.196		μs
		$f_{ADC} = f_{PCLK}/2$		5.5		1/f <sub>PCLK</sub>
t <sub>latr</sub> (2)	Trigger conversion latency	$f_{ADC} = f_{PCLK}/4 = 12 \text{ MHz}$ 0.219				μs
		f <sub>ADC</sub> = f <sub>PCLK</sub> /4		10.5		1/f <sub>PCLK</sub>
		f <sub>ADC</sub> = f <sub>HSI14</sub> = 14 MHz	0.179	-	0.250	μs
Jitter <sub>ADC</sub>	ADC jitter on trigger conversion	f <sub>ADC</sub> = f <sub>HSI14</sub>	-	1	-	1/f <sub>HSI14</sub>
ts <sup>(2)</sup>	Sampling time	f <sub>ADC</sub> = 14 MHz	0.107	-	17.1	μs
ıs. ,	Sampling time	-	1.5	-	239.5	1/f <sub>ADC</sub>
t <sub>STAB</sub> <sup>(2)</sup>	Stabilization time	-		14	•	1/f <sub>ADC</sub>
<b>,</b> (2)	Total conversion time	f <sub>ADC</sub> = 14 MHz, 12-bit resolution	1	-	18	μs
t <sub>CONV</sub> <sup>(2)</sup>	(including sampling time)	12-bit resolution	14 to 252 (t <sub>S</sub> for sampling +12.5 for successive approximation)			1/f <sub>ADC</sub>

Table 55. ADC characteristics (continued)

- 2. Guaranteed by design, not tested in production.
- 3. Specified value includes only ADC timing. It does not include the latency of the register access.
- 4. This parameter specify latency for transfer of the conversion result to the ADC\_DR register. EOC flag is set at this time.

## Equation 1: $R_{AIN}$ max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 56.  $R_{AIN}$  max for  $f_{ADC}$  = 14 MHz

T <sub>s</sub> (cycles)	t <sub>S</sub> (μs)	R <sub>AIN</sub> max (kΩ) <sup>(1)</sup>
1.5	0.11	0.4
7.5	0.54	5.9
13.5	0.96	11.4



<sup>1.</sup> During conversion of the sampled value (12.5 x ADC clock period), an additional consumption of 100  $\mu$ A on I<sub>DD</sub> and 60  $\mu$ A on I<sub>DD</sub> should be taken into account.

	All ABO	•
T <sub>s</sub> (cycles)	t <sub>S</sub> (μs)	R <sub>AIN</sub> max (kΩ) <sup>(1)</sup>
28.5	2.04	25.2
41.5	2.96	37.2
55.5	3.96	50
71.5	5.11	NA
239.5	17.1	NA

Table 56.  $R_{AIN}$  max for  $f_{ADC}$  = 14 MHz (continued)

Table 57. ADC accuracy<sup>(1)(2)(3)</sup>

Symbol	Parameter	Test conditions	Тур	Max <sup>(4)</sup>	Unit
ET	Total unadjusted error		±1.3	±2	
EO	Offset error	f <sub>PCLK</sub> = 48 MHz, f <sub>2-7</sub> = 14 MHz, P <sub>2-12</sub> < 10 kO	±1	±1.5	
EG	Gain error	$f_{ADC}$ = 14 MHz, $R_{AIN}$ < 10 kΩ $V_{DDA}$ = 3 V to 3.6 V	±0.5	±1.5	LSB
ED	Differential linearity error	T <sub>A</sub> = 25 °C	±0.7	±1	
EL	Integral linearity error		±0.8	±1.5	
ET	Total unadjusted error		±3.3	±4	
EO	Offset error	f <sub>PCLK</sub> = 48 MHz,	±1.9	±2.8	
EG	Gain error	$f_{ADC}$ = 14 MHz, $R_{AIN}$ < 10 kΩ $V_{DDA}$ = 2.7 V to 3.6 V	±2.8	±3	LSB
ED	Differential linearity error	$T_A = -40 \text{ to } 105 \text{ °C}$	±0.7	±1.3	
EL	Integral linearity error		±1.2	±1.7	
ET	Total unadjusted error		±3.3	±4	
EO	Offset error	f <sub>PCLK</sub> = 48 MHz,	±1.9	±2.8	
EG	Gain error	$f_{ADC}$ = 14 MHz, $R_{AIN}$ < 10 kΩ $V_{DDA}$ = 2.4 V to 3.6 V $T_A$ = 25 °C	±2.8	±3	LSB
ED	Differential linearity error		±0.7	±1.3	
EL	Integral linearity error		±1.2	±1.7	

<sup>1.</sup> ADC DC accuracy values are measured after internal calibration.

4. Data based on characterization results, not tested in production.

<sup>1.</sup> Guaranteed by design, not tested in production.

ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
 Any positive injection current within the limits specified for I<sub>INJ(PIN)</sub> and ΣI<sub>INJ(PIN)</sub> in Section 6.3.13 does not affect the ADC accuracy.

<sup>3.</sup> Better performance may be achieved in restricted  $V_{\text{DDA}}$ , frequency and temperature ranges.

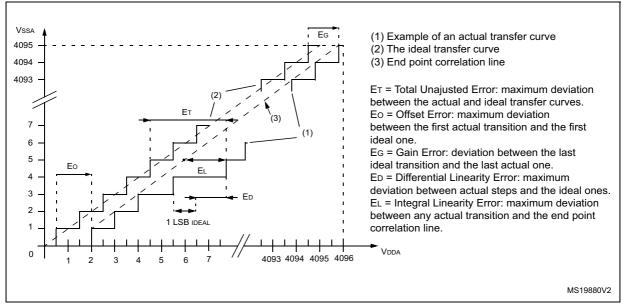
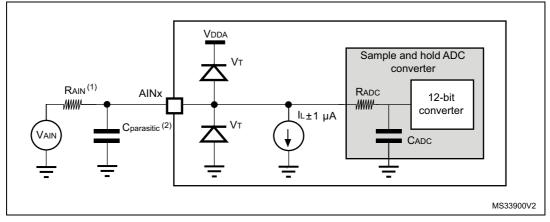


Figure 26. ADC accuracy characteristics





- Refer to Table 55: ADC characteristics for the values of RAIN, RADC and CADC.
- $C_{parasitic}$  represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high  $C_{parasitic}$  value will downgrade conversion accuracy. To remedy this,  $f_{ADC}$  should be reduced.

#### General PCB design guidelines

Power supply decoupling should be performed as shown in Figure 13: Power supply scheme. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

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# 6.3.16 DAC electrical specifications

Table 58. DAC characteristics

Symbol	Parameter	Min	Тур	Max	Unit	Comments
V <sub>DDA</sub>	Analog supply voltage for DAC ON	2.4	-	3.6	V	
R <sub>LOAD</sub> <sup>(1)</sup>	Resistive load with buffer ON	5	-	-	kΩ	Load is referred to ground
R <sub>0</sub> <sup>(1)</sup>	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and $V_{SS}$ to have a 1% accuracy is 1.5 $M\Omega$
C <sub>LOAD</sub> <sup>(1)</sup>	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min <sup>(1)</sup>	Lower DAC_OUT voltage with buffer ON	0.2	-	-	٧	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input
DAC_OUT max <sup>(1)</sup>	Higher DAC_OUT voltage with buffer ON	-	-	V <sub>DDA</sub> – 0.2	V	code (0x0E0) to (0xF1C) at $V_{DDA}$ = 3.6 V and (0x155) and (0xEAB) at $V_{DDA}$ = 2.4 V
DAC_OUT min <sup>(1)</sup>	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output
DAC_OUT max <sup>(1)</sup>	Higher DAC_OUT voltage with buffer OFF	-	-	V <sub>DDA</sub> – 1LSB	٧	excursion of the DAC.
(1)	DAC DC current	-	-	600	μA	With no load, middle code (0x800) on the input
I <sub>DDA</sub> <sup>(1)</sup>	consumption in quiescent mode <sup>(2)</sup>	-	-	700	μA	With no load, worst code (0xF1C) on the input
DNL <sup>(3)</sup>	Differential non linearity Difference between two	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration
	consecutive code-1LSB)	-	-	±2	LSB	Given for the DAC in 12-bit configuration
	Integral non linearity (difference between	-	-	±1	LSB	Given for the DAC in 10-bit configuration
INL <sup>(3)</sup>	measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±4	LSB	Given for the DAC in 12-bit configuration
	Offset error	-	-	±10	mV	
Offset <sup>(3)</sup>	(difference between measured value at Code	ı	ı	±3	LSB	Given for the DAC in 10-bit at V <sub>DDA</sub> = 3.6 V
	(0x800) and the ideal value = $V_{DDA}/2$ )	ı	-	±12	LSB	Given for the DAC in 12-bit at V <sub>DDA</sub> = 3.6 V
Gain error <sup>(3)</sup>	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration



Table 58. DAC characteristics (continued)

Symbol	Parameter	Min	Тур	Max	Unit	Comments
t <sub>SETTLING</sub> <sup>(3)</sup>	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±1LSB	-	3	4	μs	$C_{LOAD} \le 50 \text{ pF, } R_{LOAD} \ge 5 \text{ k}\Omega$
Update rate <sup>(3)</sup>	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \le 50 \text{ pF, } R_{LOAD} \ge 5 \text{ k}\Omega$
t <sub>WAKEUP</sub> (3)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	μs	$\begin{split} &C_{LOAD} \leq 50 \text{ pF, } R_{LOAD} \geq 5 \text{ k}\Omega\\ &\text{input code between lowest and}\\ &\text{highest possible ones.} \end{split}$
PSRR+ (1)	Power supply rejection ratio (to V <sub>DDA</sub> ) (static DC measurement	-	-67	-40	dB	No R <sub>LOAD</sub> , C <sub>LOAD</sub> = 50 pF

<sup>1.</sup> Guaranteed by design, not tested in production.



<sup>2.</sup> The DAC is in "quiescent mode" when it keeps the value steady on the output so no dynamic consumption is involved.

<sup>3.</sup> Data based on characterization results, not tested in production.

# 6.3.17 Comparator characteristics

Table 59. Comparator characteristics

Symbol	Parameter	Conditi	ons	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
$V_{DDA}$	Analog supply voltage	-		$V_{DD}$	-	3.6	V
V <sub>IN</sub>	Comparator input voltage range	-		0	-	$V_{DDA}$	
V <sub>SC</sub>	V <sub>REFINT</sub> scaler offset voltage	-		-	±5	±10	mV
t <sub>S_SC</sub>	V <sub>REFINT</sub> scaler startup time from power down	-		-	-	0.2	ms
t <sub>START</sub>	Comparator startup time	Startup time to reach prospecification	opagation delay	-	-	60	μs
		Ultra-low power mode		-	2	4.5	
	Propagation delay for 200 mV step with	Low power mode		-	0.7	1.5	μs
		Medium power mode		-	0.3	0.6	
	100 mV overdrive	High speed mode	V <sub>DDA</sub> ≥ 2.7 V	-	50	100	ns
		High speed mode	V <sub>DDA</sub> < 2.7 V	-	100	240	115
t <sub>D</sub>		Ultra-low power mode	•	-	2	7	
	Propagation delay for	Low power mode		-	0.7	2.1	μs
	full range step with	Medium power mode		-	0.3	1.2	
	100 mV overdrive	High speed mode	$V_{DDA} \ge 2.7 \text{ V}$	-	90	180	ns
		Trigit speed mode	V <sub>DDA</sub> < 2.7 V	-	110	300	113
V <sub>offset</sub>	Comparator offset error			ı	±4	±10	mV
dV <sub>offset</sub> /dT	Offset error temperature coefficient			-	18	1	μV/°C
		Ultra-low power mode		-	1.2	1.5	
 	COMP current	Low power mode		-	3	5	
I <sub>DD(COMP)</sub>	consumption	Medium power mode		-	10	15	μΑ
		High speed mode		-	75	100	

Table 59. Comparator characteristics (continued)

Symbol	Parameter	Condition	ons	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
		No hysteresis (COMPxHYST[1:0]=00)		-	0	-	
		Low hysteresis	High speed mode	3		13	
		(COMPxHYST[1:0]=01)	All other power modes	5	8	10	
V <sub>hys</sub>	Comparator hysteresis	Medium hysteresis	High speed mode	7		26	mV
		(COMPxHYST[1:0]=10)		9	15	19	
		High hysteresis	High speed mode	18		49	
		(COMPxHYST[1:0]=11)	All other power modes	19	31	40	

<sup>1.</sup> Data based on characterization results, not tested in production.



## 6.3.18 Temperature sensor characteristics

Table 60. TS characteristics

Symbol	Parameter	Min	Тур	Max	Unit
T <sub>L</sub> <sup>(1)</sup>	V <sub>SENSE</sub> linearity with temperature	-	±1	±2	°C
Avg_Slope <sup>(1)</sup>	Average slope	4.0	4.3	4.6	mV/°C
V <sub>30</sub>	Voltage at 30 °C (±5 °C) <sup>(2)</sup>	1.34	1.43	1.52	V
t <sub>START</sub> <sup>(1)</sup>	ADC_IN16 buffer startup time	-	-	10	μs
t <sub>S_temp</sub> <sup>(1)</sup>	ADC sampling time when reading the temperature	4	-	-	μs

<sup>1.</sup> Guaranteed by design, not tested in production.

## 6.3.19 V<sub>BAT</sub> monitoring characteristics

Table 61. V<sub>BAT</sub> monitoring characteristics

Symbol	Parameter		Тур	Max	Unit
R	Resistor bridge for V <sub>BAT</sub>	-	2 x 50	-	kΩ
Q	Ratio on V <sub>BAT</sub> measurement	-	2	-	
Er <sup>(1)</sup>	Error on Q	<b>–</b> 1	-	+1	%
t <sub>S_vbat</sub> <sup>(1)</sup>	ADC sampling time when reading the V <sub>BAT</sub>	4	-	-	μs

<sup>1.</sup> Guaranteed by design, not tested in production.

### 6.3.20 Timer characteristics

The parameters given in the following tables are guaranteed by design.

Refer to Section 6.3.13: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 62. TIMx characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>res(TIM)</sub>	Timer resolution time	-	-	1	-	t <sub>TIMxCLK</sub>
res(TIM)	Time resolution time	f <sub>TIMxCLK</sub> = 48 MHz	-	20.8	ı	ns
f	Timer external clock	-	-	f <sub>TIMxCLK</sub> /2	-	MHz
f <sub>EXT</sub>	frequency on CH1 to CH4	f <sub>TIMxCLK</sub> = 48 MHz	-	24	ı	MHz
t <sub>MAX_COUNT</sub>	16-bit timer maximum period	-	ı	2 <sup>16</sup>	ı	t <sub>TIMxCLK</sub>
		f <sub>TIMxCLK</sub> = 48 MHz	1	1365	1	μs
	32-bit counter	-	-	2 <sup>32</sup>	-	t <sub>TIMxCLK</sub>
	maximum period	f <sub>TIMxCLK</sub> = 48 MHz	-	89.48	-	S



<sup>2.</sup> Measured at  $V_{DDA}$  = 3.3 V ± 10 mV. The  $V_{30}$  ADC conversion result is stored in the TS\_CAL1 byte. Refer to *Table 2: Temperature sensor calibration values*.

Prescaler divider	PR[2:0] bits	Min timeout RL[11:0]= 0x000	Max timeout RL[11:0]= 0xFFF	Unit
/4	0	0.1	409.6	
/8	1	0.2	819.2	
/16	2	0.4	1638.4	
/32	3	0.8	3276.8	ms
/64	4	1.6	6553.6	
/128	5	3.2	13107.2	
/256	6 or 7	6.4	26214.4	

Table 63. IWDG min/max timeout period at 40 kHz (LSI)<sup>(1)</sup>

These timings are given for a 40 kHz clock but the microcontroller internal RC frequency can vary from 30 to 60 kHz. Moreover, given an exact RC oscillator frequency, the exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Table 64. WWD6 Hillimmax timeout value at 40 Hill (1 6211)						
Prescaler WDGTB		Min timeout value	Max timeout value	Unit		
1	0	0.0853	5.4613			
2	1	0.1706	10.9226	ms		
4	2	0.3413	21.8453	1115		
8	3	0.6826	43.6906			

Table 64. WWDG min/max timeout value at 48 MHz (PCLK)

## 6.3.21 Communication interfaces

## I<sup>2</sup>C interface characteristics

The I<sup>2</sup>C interface meets the timings requirements of the I<sup>2</sup>C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I<sup>2</sup>C timings requirements are guaranteed by design when the I2Cx peripheral is properly configured (refer to Reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and  $V_{\rm DDIOx}$  is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement. Refer to Section 6.3.13: I/O port characteristics for the I<sup>2</sup>C I/Os characteristics.

All I<sup>2</sup>C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:



Table 65. I<sup>2</sup>C analog filter characteristics<sup>(1)</sup>

Symbol	Symbol Parameter		Max	Unit
t <sub>AF</sub>	Maximum width of spikes that are suppressed by the analog filter	50 <sup>(2)</sup>	260 <sup>(3)</sup>	ns

- 1. Guaranteed by design, not tested in production.
- 2. Spikes with widths below t<sub>AF(min)</sub> are filtered.
- 3. Spikes with widths above  $t_{\text{AF}(\text{max})}$  are not filtered

## SPI/I<sup>2</sup>S characteristics

Unless otherwise specified, the parameters given in *Table 66* for SPI or in *Table 67* for I<sup>2</sup>S are derived from tests performed under the ambient temperature, f<sub>PCLKx</sub> frequency and supply voltage conditions summarized in *Table 23: General operating conditions*.

Refer to Section 6.3.13: I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I<sup>2</sup>S).

Table 66. SPI characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit
f <sub>SCK</sub>	SPI clock frequency	Master mode	-	18	MHz
1/t <sub>c(SCK)</sub>	SPI Clock frequency	Slave mode	-	18	IVITIZ
t <sub>r(SCK)</sub>	SPI clock rise and fall time	Capacitive load: C = 15 pF	-	6	ns
t <sub>su(NSS)</sub>	NSS setup time	Slave mode	4Tpclk	-	
t <sub>h(NSS)</sub>	NSS hold time	Slave mode	2Tpclk + 10	-	
t <sub>w(SCKH)</sub>	SCK high and low time	Master mode, f <sub>PCLK</sub> = 36 MHz, presc = 4	Tpclk/2 -2	Tpclk/2 + 1	
t <sub>su(MI)</sub>	Data input setup time	Master mode	4	-	
t <sub>su(SI)</sub>		Slave mode	5	-	
t <sub>h(MI)</sub>	Data input hold time	Master mode	4	-	
t <sub>h(SI)</sub>	Data iriput riolu tirrie	Slave mode	5	-	ns
t <sub>a(SO)</sub> (2)	Data output access time	Slave mode, f <sub>PCLK</sub> = 20 MHz	0	3Tpclk	
t <sub>dis(SO)</sub> (3)	Data output disable time	Slave mode	0	18	
t <sub>v(SO)</sub>	Data output valid time	Slave mode (after enable edge)	-	22.5	
t <sub>v(MO)</sub>	Data output valid time	Master mode (after enable edge)	-	6	
t <sub>h(SO)</sub>	Data output hold time	Slave mode (after enable edge)	11.5	-	
t <sub>h(MO)</sub>	Data output noid time	Master mode (after enable edge)	2	-	
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	25	75	%

- 1. Data based on characterization results, not tested in production.
- 2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
- 3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z



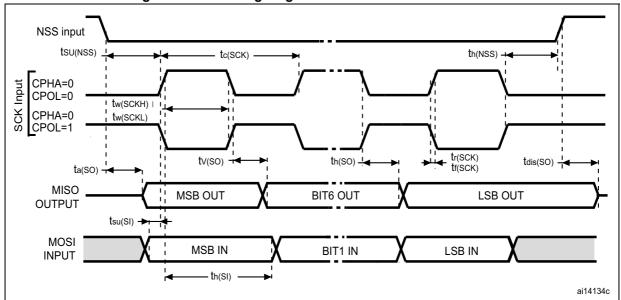
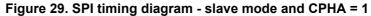
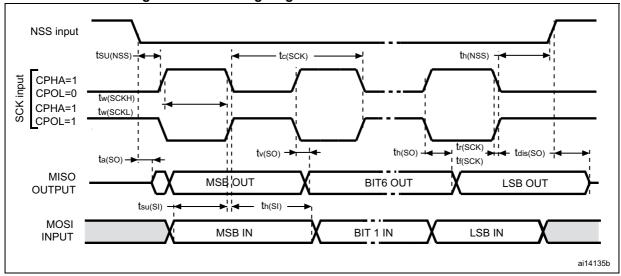


Figure 28. SPI timing diagram - slave mode and CPHA = 0





1. Measurement points are done at CMOS levels: 0.3  $V_{DD}$  and 0.7  $V_{DD}$ .

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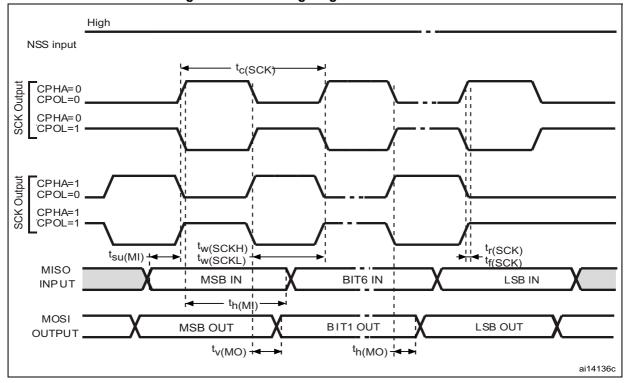


Figure 30. SPI timing diagram - master mode

1. Measurement points are done at CMOS levels: 0.3  $V_{\rm DD}$  and 0.7  $V_{\rm DD}$ .

Table 67. I<sup>2</sup>S characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit
f <sub>CK</sub>	I <sup>2</sup> S clock frequency	Master mode (data: 16 bits, Audio frequency = 48 kHz)	1.597	1.601	MHz
1/t <sub>c(CK)</sub>		Slave mode	0	6.5	
t <sub>r(CK)</sub>	I <sup>2</sup> S clock rise time	Canacitive land C = 15 pF	-	10	
t <sub>f(CK)</sub>	I <sup>2</sup> S clock fall time	Capacitive load C <sub>L</sub> = 15 pF	-	12	
t <sub>w(CKH)</sub>	I <sup>2</sup> S clock high time	Master f <sub>PCLK</sub> = 16 MHz, audio	306	-	
t <sub>w(CKL)</sub>	I <sup>2</sup> S clock low time	frequency = 48 kHz	312	-	
t <sub>v(WS)</sub>	WS valid time	Master mode	2	-	ns
t <sub>h(WS)</sub>	WS hold time	Master mode	2	-	
t <sub>su(WS)</sub>	WS setup time	Slave mode	7	-	
t <sub>h(WS)</sub>	WS hold time	Slave mode	0	-	
DuCy(SCK)	I <sup>2</sup> S slave input clock duty cycle	Slave mode	25	75	%

Symbol	Parameter	Conditions	Min	Max	Unit
t <sub>su(SD_MR)</sub>	Data input setup time	Master receiver	6	-	
t <sub>su(SD_SR)</sub>	Data input setup time	Slave receiver	2	-	
t <sub>h(SD_MR)</sub> <sup>(2)</sup>	Data input hold time	Master receiver	4	-	
t <sub>h(SD_SR)</sub> (2)	Data input noid time	Slave receiver	0.5	-	no
t <sub>v(SD_MT)</sub> <sup>(2)</sup>	Data output valid time	Master transmitter	-	4	ns
t <sub>v(SD_ST)</sub> <sup>(2)</sup>	Data output valid time	Slave transmitter	-	31	
t <sub>h(SD_MT)</sub>	Data output hold time	Master transmitter	0	-	
t <sub>h(SD_ST)</sub>	Data output hold time	Slave transmitter	13	-	

Table 67. I<sup>2</sup>S characteristics<sup>(1)</sup> (continued)

- 1. Data based on design simulation and/or characterization results, not tested in production.
- 2. Depends on  $f_{PCLK}$ . For example, if  $f_{PCLK}$  = 8 MHz, then  $T_{PCLK}$  = 1/ $f_{PLCLK}$  = 125 ns.

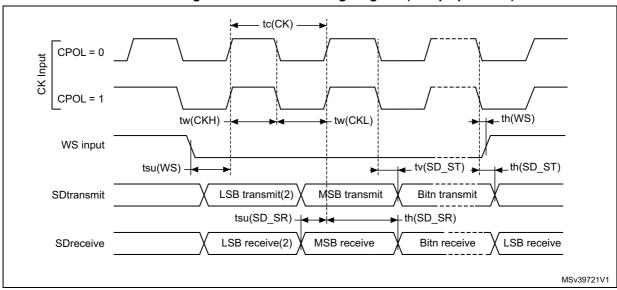


Figure 31. I<sup>2</sup>S slave timing diagram (Philips protocol)

- 1. Measurement points are done at CMOS levels:  $0.3 \times V_{DDIOx}$  and  $0.7 \times V_{DDIOx}$
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

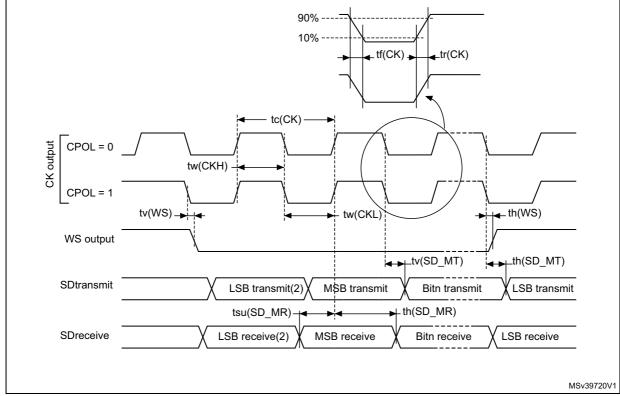


Figure 32. I<sup>2</sup>S master timing diagram (Philips protocol)

- 1. Data based on characterization results, not tested in production.
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

## CAN (controller area network) interface

Refer to Section 6.3.13: I/O port characteristics for more details on the input/output alternate function characteristics (CAN\_TX and CAN\_RX).

# 7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

## 7.1 UFBGA100 package information

UFBGA100 is a 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra-fine-profile ball grid array package.

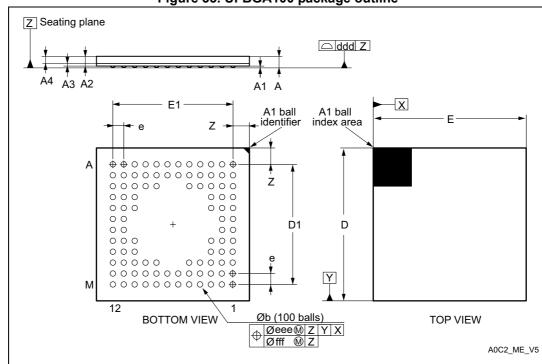


Figure 33. UFBGA100 package outline

1. Drawing is not to scale.

Table 68. UFBGA100 package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.450	-	-	0.0177	-
A3	-	0.130	-	-	0.0051	0.0094
A4	-	0.320	-	-	0.0126	-

inches<sup>(1)</sup> millimeters Symbol Min. Тур. Max. Min. Тур. Max. 0.240 0.290 0.340 0.0094 0.0114 0.0134 b D 6.850 7.000 7.150 0.2697 0.2756 0.2815 5.500 0.2165 D1 Ε 0.2697 6.850 7.000 7.150 0.2756 0.2815 E1 5.500 0.2165 е 0.500 0.0197 Ζ 0.750 0.0295 ddd 0.080 0.0031 eee 0.150 0.0059 fff 0.050 0.0020

Table 68. UFBGA100 package mechanical data (continued)

Figure 34. Recommended footprint for UFBGA100 package

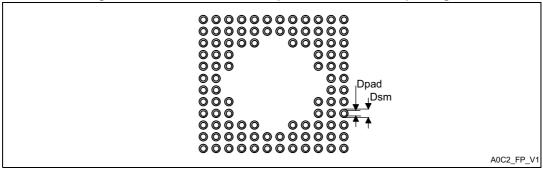


Table 69. UFBGA100 recommended PCB design rules

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the solder mask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

## **Device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

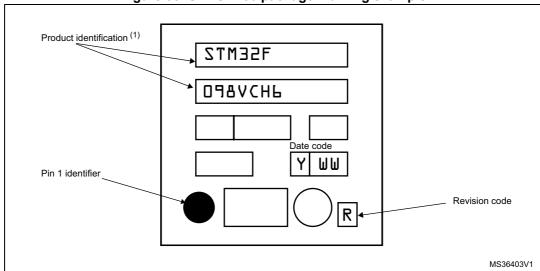


Figure 35. UFBGA100 package marking example

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



#### 7.2 LQFP100 package information

LQFP100 is a100-pin, 14 x 14 mm low-profile quad flat package.

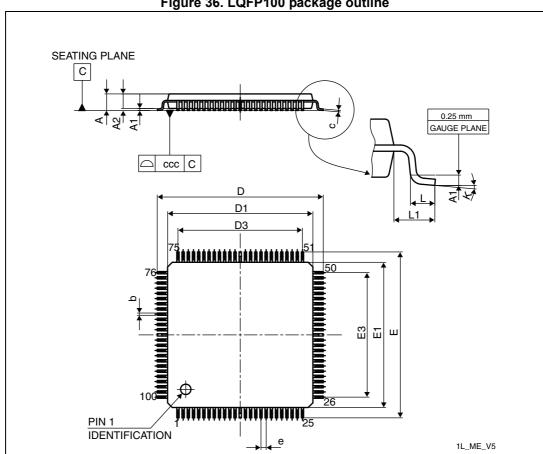


Figure 36. LQFP100 package outline

1. Drawing is not to scale.

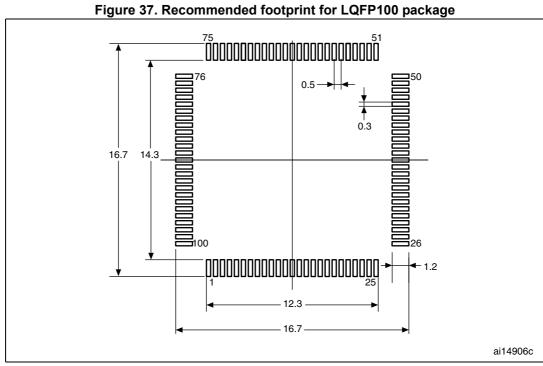
Table 70. LQPF100 package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
Е	15.800	16.000	16.200	0.6220	0.6299	0.6378

0		millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max	
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591	
E3	-	12.000	-	-	0.4724	-	
е	-	0.500	-	-	0.0197	-	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295	
L1	-	1.000	-	-	0.0394	-	
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°	
CCC	-	-	0.080	-	-	0.0031	

Table 70. LQPF100 package mechanical data (continued)

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.



Dimensions are expressed in millimeters.

## **Device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Product identification (1)

STM32F098

Revision code

VCTL

Pin 1 identifier

MS35582V1

Figure 38. LQFP100 package marking example

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



## 7.3 UFBGA64 package information

UFBGA64 is a 64-ball, 5 x 5 mm, 0.5 mm pitch ultra-fine-profile ball grid array package.

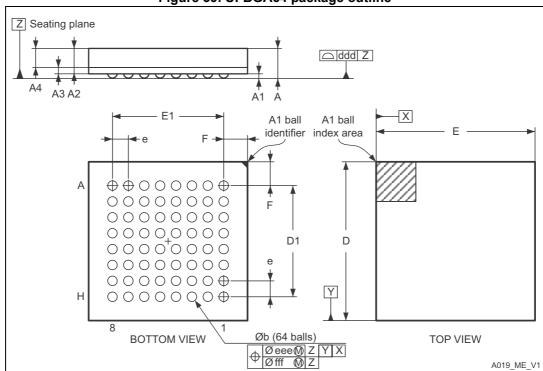


Figure 39. UFBGA64 package outline

1. Drawing is not to scale.

Table 71. UFBGA64 package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Тур	Max	Min	Тур	Max
Α	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A3	0.080	0.130	0.180	0.0031	0.0051	0.0071
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146
b	0.170	0.280	0.330	0.0067	0.0110	0.0130
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	3.450	3.500	3.550	0.1358	0.1378	0.1398
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	3.450	3.500	3.550	0.1358	0.1378	0.1398
е	-	0.500	-	-	0.0197	-
F	0.700	0.750	0.800	0.0276	0.0295	0.0315

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inches<sup>(1)</sup> millimeters **Symbol** Min Тур Max Min Тур Max 0.530 0.0209 0.0236 Α 0.460 0.600 0.0181 ddd 0.080 0.0031 0.150 0.0059 eee fff 0.050 0.0020

Table 71. UFBGA64 package mechanical data (continued)

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

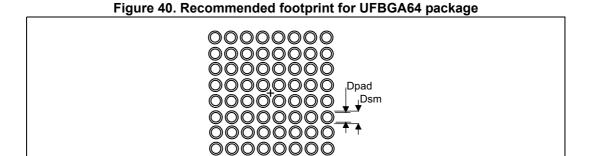


Table 72. UFBGA64 recommended PCB design rules

Dimension	Recommended values		
Pitch	0.5		
Dpad	0.280 mm		
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)		
Stencil opening	0.280 mm		
Stencil thickness	Between 0.100 mm and 0.125 mm		
Pad trace width	0.100 mm		

## **Device marking**

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

A019\_FP\_V2

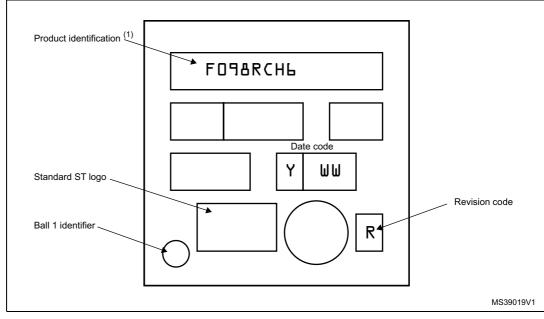


Figure 41. UFBGA64 package marking example

Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet
qualified and therefore not yet ready to be used in production and any consequences deriving from such
usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering
samples in production. ST Quality has to be contacted prior to any decision to use these Engineering
Samples to run qualification activity.

# 7.4 WLCSP64 package information

WLCSP64 is a 64-ball, 3.347 x 3.585 mm, 0.4 mm pitch wafer-level chip-scale package.

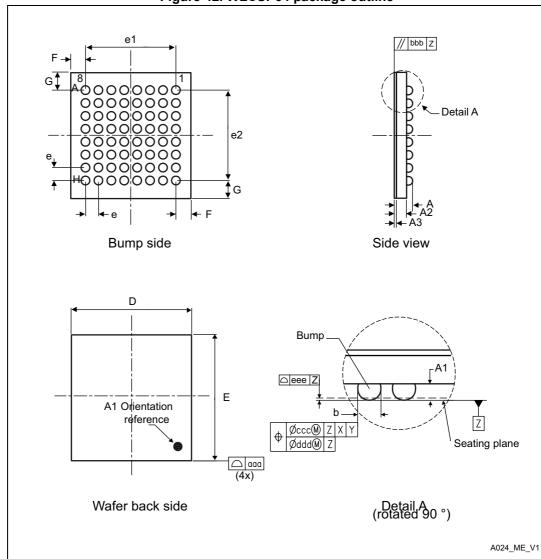


Figure 42. WLCSP64 package outline

1. Drawing is not to scale.

Table 73. WLCSP64 package mechanical data

1 0						
Symbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3	-	0.025	-	-	0.0010	-



Symbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Typ 0.0098 0.1318 0.1411 0.0157 0.1102 0.1102	Max
b <sup>(2)</sup>	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	3.312	3.347	3.382	0.1304	0.1318	0.1331
Е	3.550	3.585	3.620	0.1398	0.1411	0.1425
е	-	0.400	-	-	0.0157	-
e1	-	2.800	-	-	0.1102	-
e2	-	2.800	-	-	0.1102	-
F	-	0.2735	-	-	0.0108	-
G	-	0.3925	-	-	0.0155	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

Table 73. WLCSP64 package mechanical data (continued)

- 1. Values in inches are converted from mm and rounded to 4 decimal digits.
- 2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

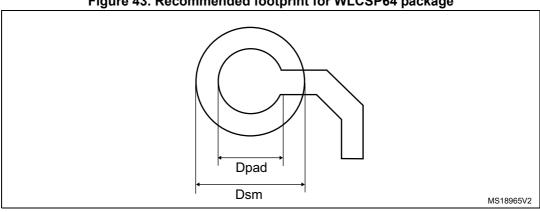


Figure 43. Recommended footprint for WLCSP64 package

Table 74. WLCSP64 recommended PCB design rules

Dimension	Recommended values
Pitch	0.4
Dpad	260 μm max. (circular)
рац	220 µm recommended
Dsm	300 μm min. (for 260 μm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed.

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The following figure gives an example of topside marking orientation versus ball A1 identifier location.

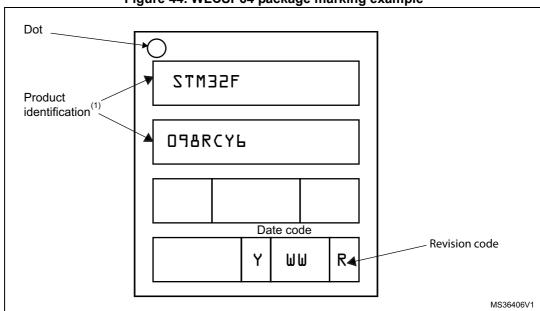


Figure 44. WLCSP64 package marking example

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

# 7.5 LQFP64 package information

LQFP64 is a 64-pin, 10 x 10 mm low-profile quad flat package.

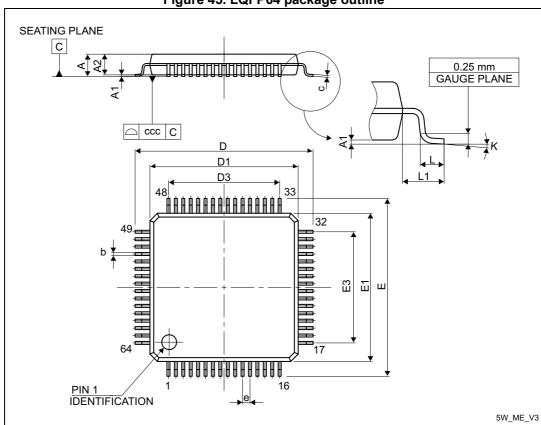


Figure 45. LQFP64 package outline

1. Drawing is not to scale.

Table 75. LQFP64 package mechanical data

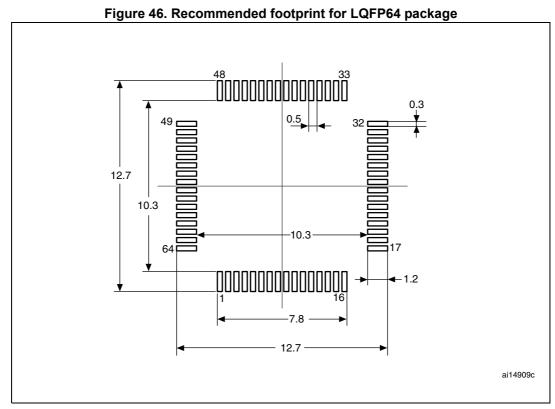
rabio 70. Eq. 1 04 packago mochamour ada						
Cumbal	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
Е	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

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inches<sup>(1)</sup> millimeters **Symbol** Min Typ Max Min Тур Max 7.500 0.2953 E3 0.500 0.0197 е 0° 7° 0° 7° K  $3.5^{\circ}$  $3.5^{\circ}$ L 0.450 0.600 0.750 0.0177 0.0236 0.0295 L1 1.000 0.0394 0.080 0.0031 CCC

Table 75. LQFP64 package mechanical data (continued)

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.



1. Dimensions are expressed in millimeters.

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

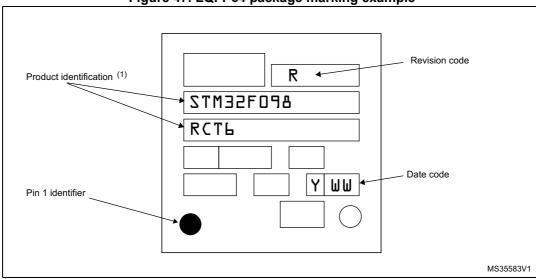


Figure 47. LQFP64 package marking example

Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet
qualified and therefore not yet ready to be used in production and any consequences deriving from such
usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering
samples in production. ST Quality has to be contacted prior to any decision to use these Engineering
Samples to run qualification activity.



# 7.6 LQFP48 package information

LQFP48 is a 48-pin, 7 x 7 mm low-profile quad flat package.

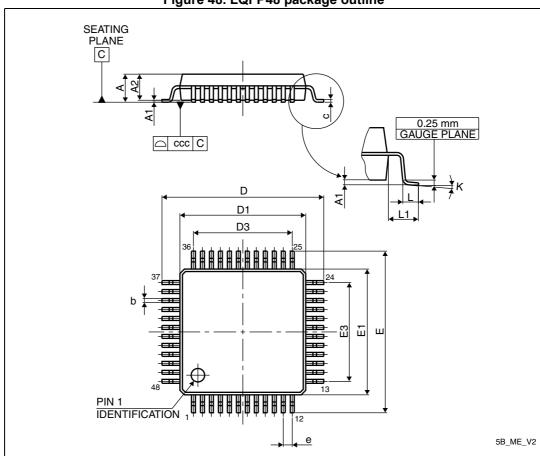


Figure 48. LQFP48 package outline

1. Drawing is not to scale.

Table 76. LQFP48 package mechanical data

Symbol		millimeters	inches <sup>(1)</sup>				
Symbol	Min	Тур	Max	Min	Тур	Max	
Α	-	-	1.600	-	-	0.0630	
A1	0.050	-	0.150	0.0020	-	0.0059	
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571	
b	0.170	0.220	0.270	0.0067	0.0087	0.0106	
С	0.090	-	0.200	0.0035	-	0.0079	
D	8.800	9.000	9.200	0.3465	0.3543	0.3622	
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835	
D3	-	5.500	-	-	0.2165	-	
Е	8.800	9.000	9.200	0.3465	0.3543	0.3622	
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835	
E3	-	5.500	-	-	0.2165	-	
е	-	0.500	-	-	0.0197	-	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295	
L1	-	1.000	-	-	0.0394	-	
k	0°	3.5°	7°	0°	3.5°	7°	
ccc	-	-	0.080	-	-	0.0031	

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 49. Recommended footprint for LQFP48 package 9.70 ai14911d

1. Dimensions are expressed in millimeters.

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The following figure gives an example of topside marking orientation versus pin 1 identifier location.

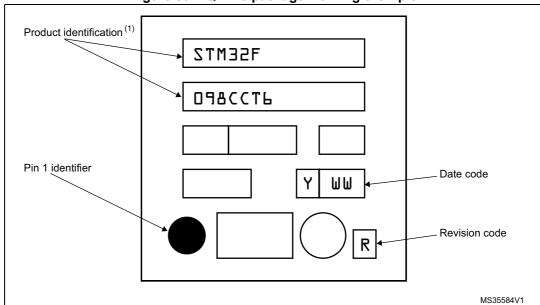


Figure 50. LQFP48 package marking example

<sup>1.</sup> Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

# 7.7 UFQFPN48 package information

UFQFPN48 is a 48-lead, 7x7 mm, 0.5 mm pitch, ultra-thin fine-pitch quad flat package.

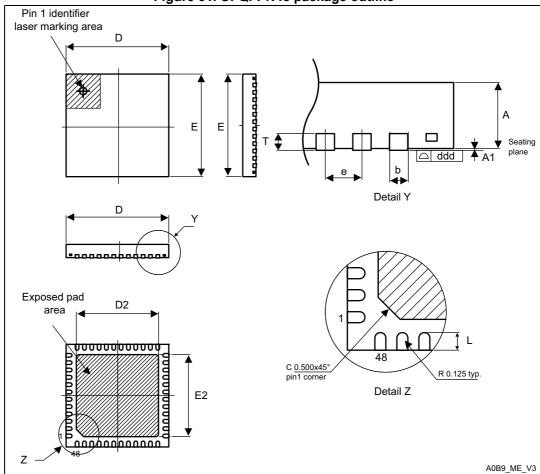


Figure 51. UFQFPN48 package outline

- 1. Drawing is not to scale.
- 2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
- There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

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Table 77. UFQFPN48 package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
D	6.900	7.000	7.100	0.2717	0.2756	0.2795
E	6.900	7.000	7.100	0.2717	0.2756	0.2795
D2	5.500	5.600	5.700	0.2165	0.2205	0.2244
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
Т	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
е	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

7.30

0.20

0.30

0.30

0.55

0.560

0.55

0.560

0.55

0.560

0.55

0.75

0.75

0.75

1. Dimensions are expressed in millimeters.

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

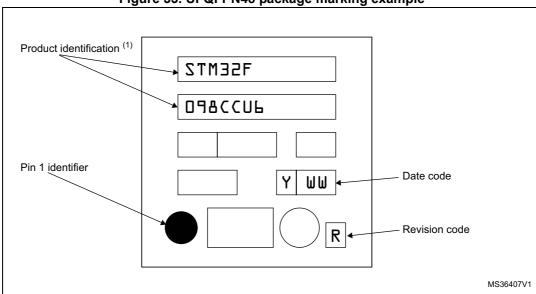


Figure 53. UFQFPN48 package marking example

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



## 7.8 Thermal characteristics

The maximum chip junction temperature (T<sub>J</sub>max) must never exceed the values given in *Table 23: General operating conditions*.

The maximum chip-junction temperature,  $T_J$  max, in degrees Celsius, may be calculated using the following equation:

$$T_J \max = T_A \max + (P_D \max x \Theta_{JA})$$

#### Where:

- T<sub>A</sub> max is the maximum ambient temperature in °C,
- Θ<sub>IA</sub> is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D$  max is the sum of  $P_{INT}$  max and  $P_{I/O}$  max ( $P_D$  max =  $P_{INT}$  max +  $P_{I/O}$ max),
- P<sub>INT</sub> max is the product of I<sub>DD</sub> and V<sub>DD</sub>, expressed in Watts. This is the maximum chip internal power.

P<sub>I/O</sub> max represents the maximum power dissipation on output pins where:

$$P_{I/O}$$
 max =  $\Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DDIOx} - V_{OH}) \times I_{OH})$ ,

taking into account the actual  $V_{OL}$  /  $I_{OL}$  and  $V_{OH}$  /  $I_{OH}$  of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit
	Thermal resistance junction-ambient UFBGA100 - 7 × 7 mm	55	
	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm	42	
	Thermal resistance junction-ambient UFBGA64 - 5 × 5 mm / 0.5 mm pitch	65	
$\Theta_{\sf JA}$	Thermal resistance junction-ambient LQFP64 - 10 × 10 mm / 0.5 mm pitch	44	°C/W
	Thermal resistance junction-ambient WLCSP64 - 0.4 mm pitch	53	
	Thermal resistance junction-ambient LQFP48 - 7 × 7 mm	54	
	Thermal resistance junction-ambient UFQFPN48 - 7 × 7 mm	32	

Table 78. Package thermal characteristics

### 7.8.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

## 7.8.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Section 8: Part numbering*.



Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F098CC/RC/VC at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

### **Example 1: High-performance application**

Assuming the following application conditions:

Maximum temperature  $T_{Amax}$  = 82 °C (measured according to JESD51-2),  $I_{DDmax}$  = 50 mA,  $V_{DD}$  = 3.5 V, maximum 20 I/Os used at the same time in output at low level with  $I_{OL}$  = 8 mA,  $V_{OL}$ = 0.4 V and maximum 8 I/Os used at the same time in output at low level with  $I_{OL}$  = 20 mA,  $V_{OL}$ = 1.3 V

 $P_{INTmax}$  = 50 mA × 3.5 V= 175 mW

 $P_{IOmax} = 20 \times 8 \text{ mA} \times 0.4 \text{ V} + 8 \times 20 \text{ mA} \times 1.3 \text{ V} = 272 \text{ mW}$ 

This gives: P<sub>INTmax</sub> = 175 mW and P<sub>IOmax</sub> = 272 mW:

 $P_{Dmax} = 175 + 272 = 447 \text{ mW}$ 

Using the values obtained in *Table 78*  $T_{Jmax}$  is calculated as follows:

For LQFP64, 45 °C/W

$$T_{\text{lmax}}$$
 = 82 °C + (45 °C/W × 447 mW) = 82 °C + 20.115 °C = 102.115 °C

This is within the range of the suffix 6 version parts ( $-40 < T_J < 105$  °C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see Section 8: Part numbering).

Note:

With this given  $P_{Dmax}$  we can find the  $T_{Amax}$  allowed for a given device temperature range (order code suffix 6 or 7).

Suffix 6: 
$$T_{Amax} = T_{Jmax} - (45^{\circ}\text{C/W} \times 447 \text{ mW}) = 105\text{-}20.115 = 84.885 ^{\circ}\text{C}$$
  
Suffix 7:  $T_{Amax} = T_{Jmax} - (45^{\circ}\text{C/W} \times 447 \text{ mW}) = 125\text{-}20.115 = 104.885 ^{\circ}\text{C}$ 

#### **Example 2: High-temperature application**

Using the same rules, it is possible to address applications that run at high temperatures with a low dissipation, as long as junction temperature  $T_J$  remains within the specified range.

Assuming the following application conditions:

Maximum temperature  $T_{Amax}$  = 100 °C (measured according to JESD51-2),  $I_{DDmax}$  = 20 mA,  $V_{DD}$  = 3.5 V, maximum 20 I/Os used at the same time in output at low level with  $I_{OL}$  = 8 mA,  $V_{OL}$  = 0.4 V

 $P_{INTmax}$  = 20 mA × 3.5 V= 70 mW

 $P_{IOmax} = 20 \times 8 \text{ mA} \times 0.4 \text{ V} = 64 \text{ mW}$ 

This gives:  $P_{INTmax} = 70 \text{ mW}$  and  $P_{IOmax} = 64 \text{ mW}$ :

 $P_{Dmax} = 70 + 64 = 134 \text{ mW}$ 

Thus: P<sub>Dmax</sub> = 134 mW

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Using the values obtained in  $Table 78 T_{Jmax}$  is calculated as follows:

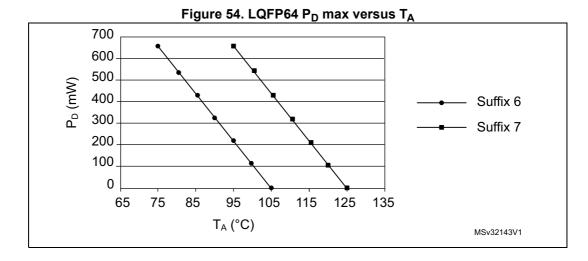
For LQFP64, 45 °C/W

$$T_{Jmax}$$
 = 100 °C + (45 °C/W × 134 mW) = 100 °C + 6.03 °C = 106.03 °C

This is above the range of the suffix 6 version parts ( $-40 < T_J < 105$  °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see *Section 8: Part numbering*) unless we reduce the power dissipation in order to be able to use suffix 6 parts.

Refer to the figure below to select the required temperature range (suffix 6 or 7) according to your temperature or power requirements.



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# 8 Part numbering

For a list of available options (memory, package, and so on) or for further information on any aspect of this device, please contact your nearest ST sales office.

Table 79. Ordering information scheme 098 Example: STM32 R С **Device family** STM32 = ARM-based 32-bit microcontroller **Product type** F = General-purpose **Sub-family** 098 = STM32F098xx Pin count C = 48 pins R = 64 pins V = 100 pins User code memory size C = 256 Kbyte **Package** H = UFBGA T = LQFPU = UFQFPN Y = WLCSP Temperature range  $6 = -40 \text{ to } 85 \,^{\circ}\text{C}$ **Options** xxx = code ID of programmed parts (includes packing type)

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TR = tape and reel packing

blank = tray packing

# 9 Revision history

Table 80. Document revision history

Date	Revision	Changes
10-Nov-2014	1	Initial release.
19-Nov-2014	2	Updated:  - Section: Features on the cover page: changed the number of capacitive sensing channels.  - Table: STM32F098xC family device features and peripheral counts: changed the number of GPIOs and capacitive sensing channels.
		Cover page:  - the document status to Datasheet - Production data  - Fast Mode Plus current sink corrected from 20 mA to "extra"  Section 2: Description:  - Table 1: STM32F098CC/RC/VC family device features and peripheral counts- I/O and capacitive channel numbers corrected  Section 3: Functional overview:  - updated Figure 1: Block diagram (number of AF) and
17-Dec-2015	3	Figure 2: Clock tree  - Section 3.5.3: Low-power modes - added info. on comm. peripherals configurable to operate with HSI  - Section 3.9.2: Extended interrupt/event controller (EXTI) - number of GPIOs corrected  - added number of complementary outputs for the general purpose and for the advance control timers in Table 6: Timer feature comparison  - Section 3.14.3: Basic timersTIM6 and TIM7 - corrected from plain text to numbered title
		Section 4: Pinouts and pin descriptions:  - Package pinout figures updated (look and feel)  - Figure 7: WLCSP64 package pinout - now presented in top view  - Table 12: STM32F098CC/RC/VC pin definitions - MCO moved from additional to alternate functions column  - Table 14: Alternate functions selected through GPIOB_AFR registers for port B- CAN_RX and CAN-TX added as AF4 for PB8 and PB9, respectively  - Table 18: Alternate functions selected through GPIOF_AFR registers for port F- lines PF4 and PF5 removed  Section 5: Memory mapping:
		<ul> <li>updated Figure 10: STM32F098CC/RC/VC memory map</li> </ul>



Table 80. Document revision history (continued)

Section 6: Electrical characteristics:	
- footnote for V <sub>IN</sub> max value in Table 20: \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	voltage: i-40°-to-85° ite 768 kHz i-OUT to to fLSE gs updated ind TTa I/O e volt tolerant  removed I some dded  mption) in min value me minimum rameter name VBAT I Res <sub>TM</sub> i Typ column, values defined d and max inilips protocol) s and ated g example and example and

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